

# Space-Grade High-Performance Serial Persistent SRAM Memory

(AS1016A04, AS3016A04)

## Features

- Interface
  - Serial Peripheral Interface QSPI (4-4-4)
    - Single Data Rate Mode: 54MHz
- Technology
  - 40nm pMTJ STT-MRAM
    - Virtually unlimited Endurance and Data Retention (see **Endurance & Retention** : Table 31)
- Density
  - 16Mb
- Operating Voltage Range
  - $V_{CC}$ : 1.71V – 2.00V
  - $V_{CC}$ : 2.70V – 3.60V
- Operating Temperature Range
  - Industrial Extended -40°C to 125°C
- Packages
  - 8-pad WSON (5.0mm x 6.0mm)
  - 8-pin SOIC (5.2mm x 5.2mm)
- Data Protection
  - Hardware Based
    - Write Protect Pin (WP#)
  - Software Based
    - Address Range Selectable through Configuration bits (Top/Bottom, Block Protect[2:0])
- Identification
  - 64-bit Unique ID
  - 64-bit User Programmable Serial Number
- Augmented Storage Array
  - 256-byte User Programmable with Write Protection
- Supports JEDEC Reset
- 48-hour burn-in at 125°C
- RoHS & REACH Compliant

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## General Description

ASx016A04 is a magneto-resistive random-access memory (MRAM). It is offered in 16Mbit density. MRAM technology is analogous to Flash technology with SRAM compatible read/write timings (Persistent SRAM, P-SRAM). Data is always non-volatile with  $10^{16}$  write cycles endurance and 1000 years data retention at 85°C.

**Figure 1: Technology Comparison**

|                          | SRAM | Flash | EEPROM | MRAM |
|--------------------------|------|-------|--------|------|
| <b>Non-Volatility</b>    | –    | √     | √      | √    |
| <b>Write Performance</b> | √    | –     | –      | √    |
| <b>Read Performance</b>  | √    | –     | –      | √    |
| <b>Endurance</b>         | √    | –     | –      | √    |
| <b>Power</b>             | –    | –     | –      | √    |

MRAM is a true random-access memory; allowing both reads and writes to occur randomly in memory. MRAM is ideal for applications that must store and retrieve data without incurring large latency penalties. It offers low latency, low power, infinite endurance and scalable non-volatile memory technology.

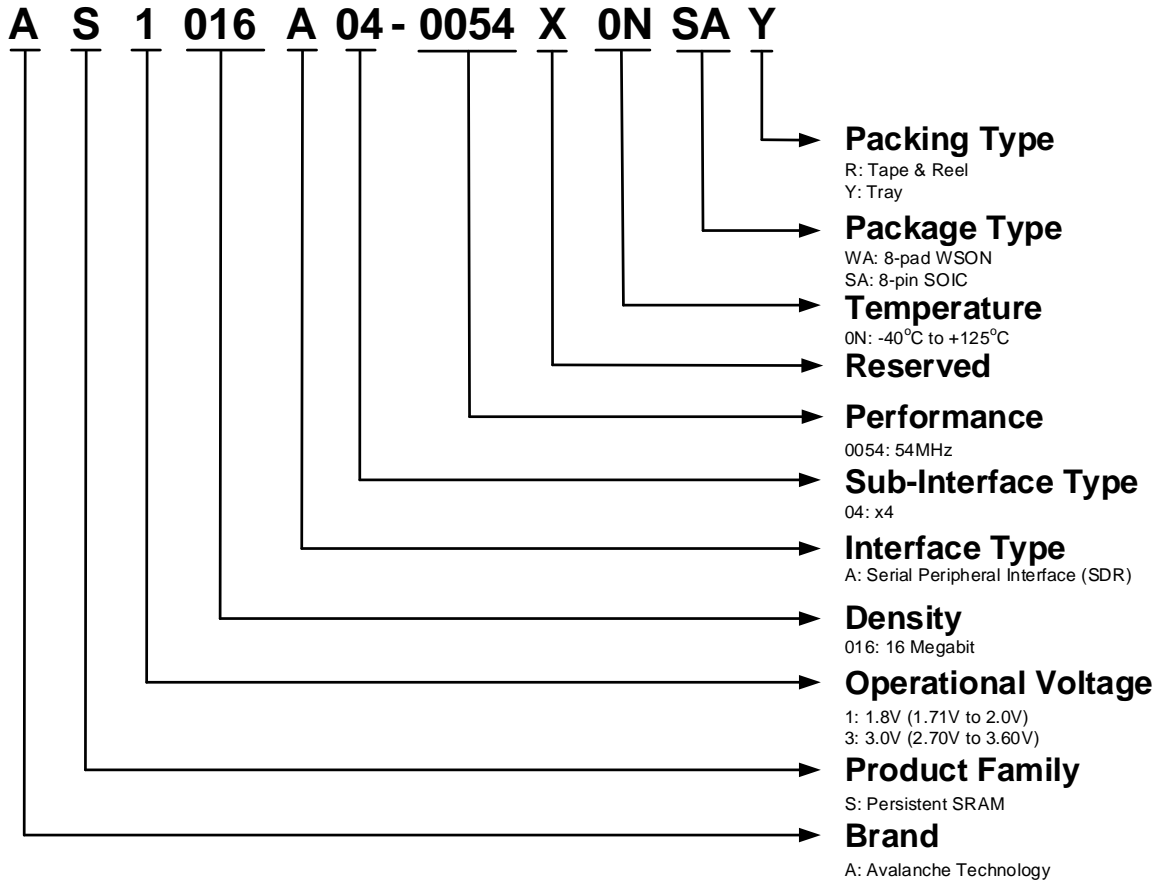
ASx016A04 has a Serial Peripheral Interface (SPI). SPI is a synchronous interface which uses separate lines for data and clock to help keep the host and slave in perfect synchronization. The clock tells the receiver exactly when to sample the bits on the data line. This can be either the rising (low to high) or falling (high to low) or both edges of the clock signal; please consult the instruction sequences in this datasheet for more details. When the receiver detects that correct edge, it can latch in the data.

ASx016A04 is available in small footprint 8-pad WSON and 8-pin SOIC packages. These packages are compatible with similar low-power volatile and non-volatile products.

ASx016A04 has been tested at -40°C to 125°C operating temperature range and 48-hour burn-in at 125°C.

## Ordering Options

The ordering part numbers are formed by a valid combination of the following options:



## Valid Combinations — Space-Grade

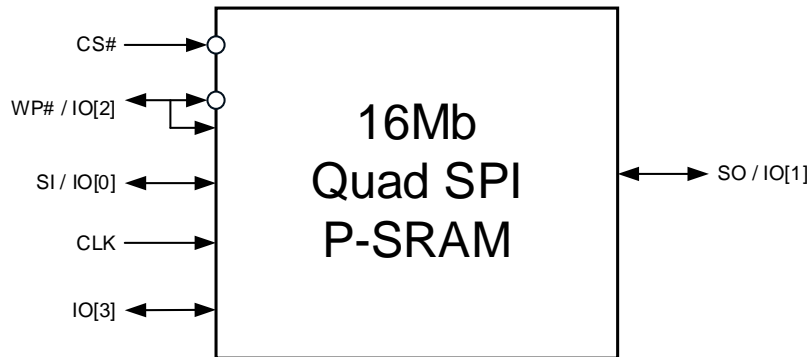
Valid Combinations list includes device configurations currently available. Contact your local sales office to confirm availability of specific valid combinations and to check on newly released combinations.

**Table 1: Valid Combinations List**

| Valid Combinations – 54MHz |                   |              |              |                       |
|----------------------------|-------------------|--------------|--------------|-----------------------|
| Base Part Number           | Temperature Range | Package Type | Packing Type | Part Number           |
| AS1016A04-0054X            | 0N                | WA, SA       | R, Y         | AS1016A04-0054X0NSWAR |
|                            |                   |              |              | AS1016A04-0054X0NWAY  |
|                            |                   |              |              | AS1016A04-0054X0NSAR  |
|                            |                   |              |              | AS1016A04-0054X0NSAY  |
| AS3016A04-0054X            | 0N                | WA, SA       | R, Y         | AS3016A04-0054X0NSWAR |
|                            |                   |              |              | AS3016A04-0054X0NWAY  |
|                            |                   |              |              | AS3016A04-0054X0NSAR  |
|                            |                   |              |              | AS3016A04-0054X0NSAY  |

## Signal Description and Assignment

**Figure 2: Device Pinout**



**Table 2: Signal Description**

| Signal             | Type                        | Description   |
|--------------------|-----------------------------|---|
| <b>CS#</b>         | Input                       | <b>Chip Select:</b> When CS# is driven High, the device will enter standby mode. All other input pins are ignored and the output pin is tri-stated. Driving CS# Low enables the device, placing it in the active mode. After power-up, a falling edge on CS# is required prior to the start of any instructions.  |
| <b>WP# / IO[2]</b> | Input<br>/<br>Bidirectional | <b>Write Protect (SPI):</b> Write protects the status register in conjunction with the enable/disable bit of the status register. This is important since other write protection features are controlled through the Status Register. When the enable/disable bit of the status register is set to 1 and the WP# signal is driven Low, the status register becomes read-only and the WRITE STATUS REGISTER operation will not execute. This signal does not have internal pull-ups, it cannot be left floating and must be driven. WP# is valid only in Single SPI mode. This pin can be tied to Vcc if not used.<br><b>Bidirectional Data 2 (DPI/QPI):</b> The bidirectional I/O transfers data into and out of the device in Dual and Quad SPI modes.                                       |
| <b>CLK</b>         | Input                       | <b>Clock:</b> Provides the timing for the serial interface. Depending on the mode selected, either single (rising or falling) edge or both edges of the clock are utilized for information transfer.<br>In Single Data Rate mode (SDR) command, address and data inputs are latched on the rising edge of the clock. Data is output on the falling edge of the clock.<br>In Double Data Rate mode (DDR) command is latched on the rising edge of the clock. Address and Data inputs are latched on both edges of the clock. Similarly, Data is output on both edges of the clock.<br>The following two SPI clock modes are supported. <ul style="list-style-type: none"> <li>• SPI Mode 0 (CPOL = 0, CPHA = 0) – SDR and DDR</li> <li>• SPI Mode 3 (CPOL = 1, CPHA = 1) – SDR only</li> </ul> |
| <b>IO[3]</b>       | Bidirectional               | <b>Bidirectional Data 3 (DPI/QPI):</b> The bidirectional I/O transfers data into and out of the device in Dual and Quad SPI modes. This pin can be tied to Vcc if not used.   |

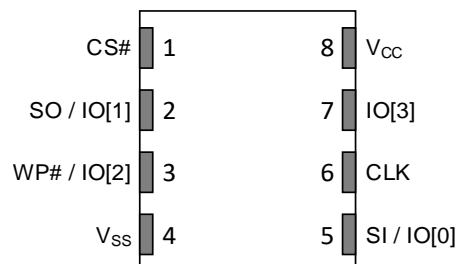


| Signal          | Type                         | Description  |
|-----------------|------------------------------|--|
| SI / IO[0]      | Input<br>/<br>Bidirectional  | <b>Serial Data Input (SPI):</b> The unidirectional I/O transfers data into the device on the rising edge of the clock in Single SPI mode.<br><b>Bidirectional Data 0 (DPI/QPI):</b> The bidirectional I/O transfers data into and out of the device in Dual and Quad SPI modes.          |
| SO / IO[1]      | Output<br>/<br>Bidirectional | <b>Serial Data Output (SPI):</b> The unidirectional I/O transfers data out of the device on the falling edge of the clock in Single SPI mode.<br><b>Bidirectional Data 1 (DPI/QPI):</b> The bidirectional I/O that transfers data into and out of the device in Dual and Quad SPI modes. |
| V <sub>cc</sub> | Supply                       | V <sub>cc</sub> : Core and I/O power supply.   |
| V <sub>ss</sub> | Supply                       | V <sub>ss</sub> : Core and I/O ground supply.  |

## Package Options

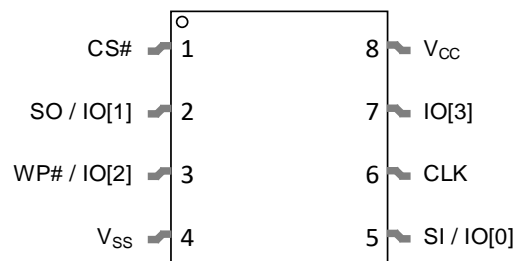
### 8-Pad WSON (Top View)

**Figure 3: 8-Pad WSON**



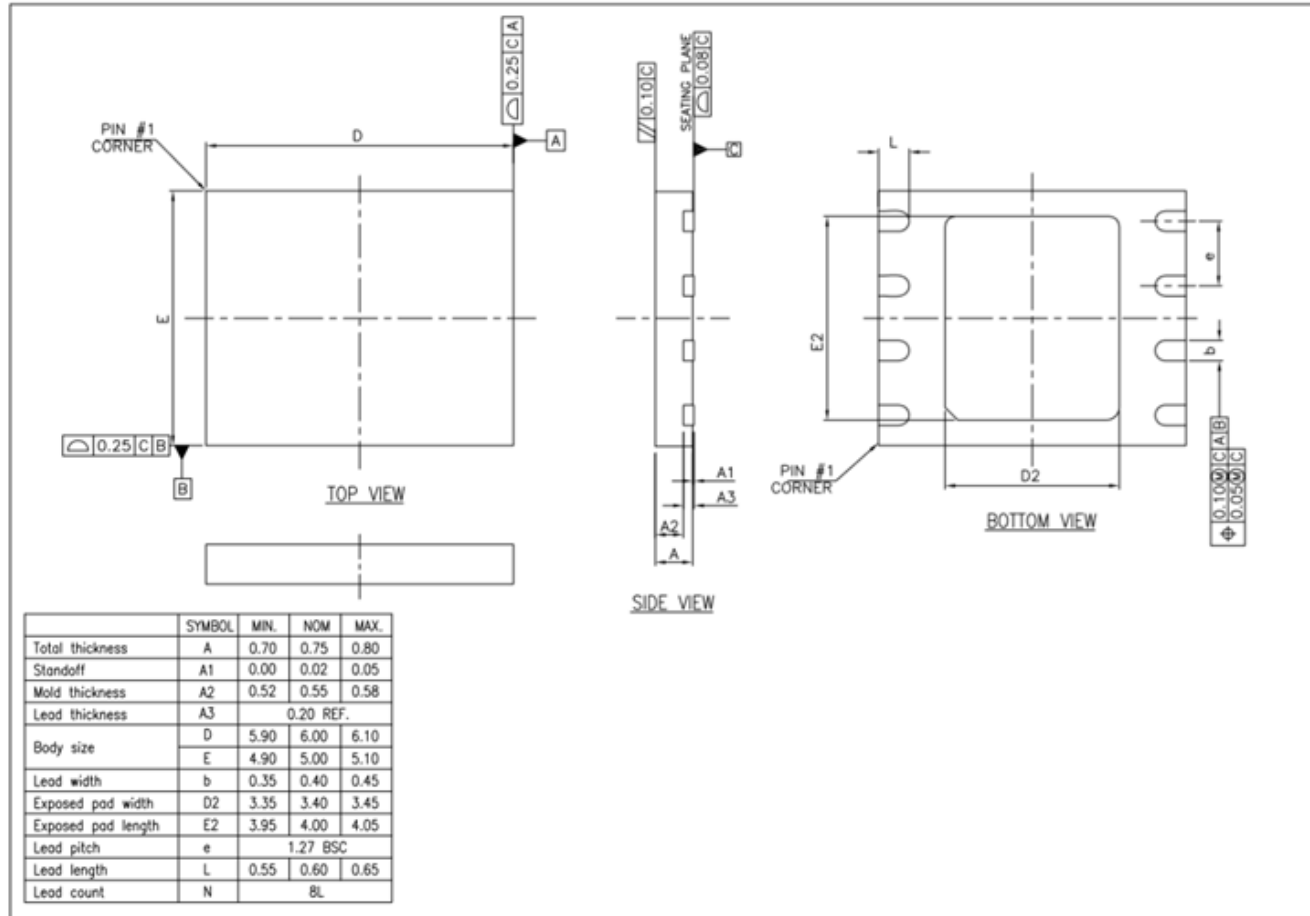
### 8-Pin SOIC (Top View)

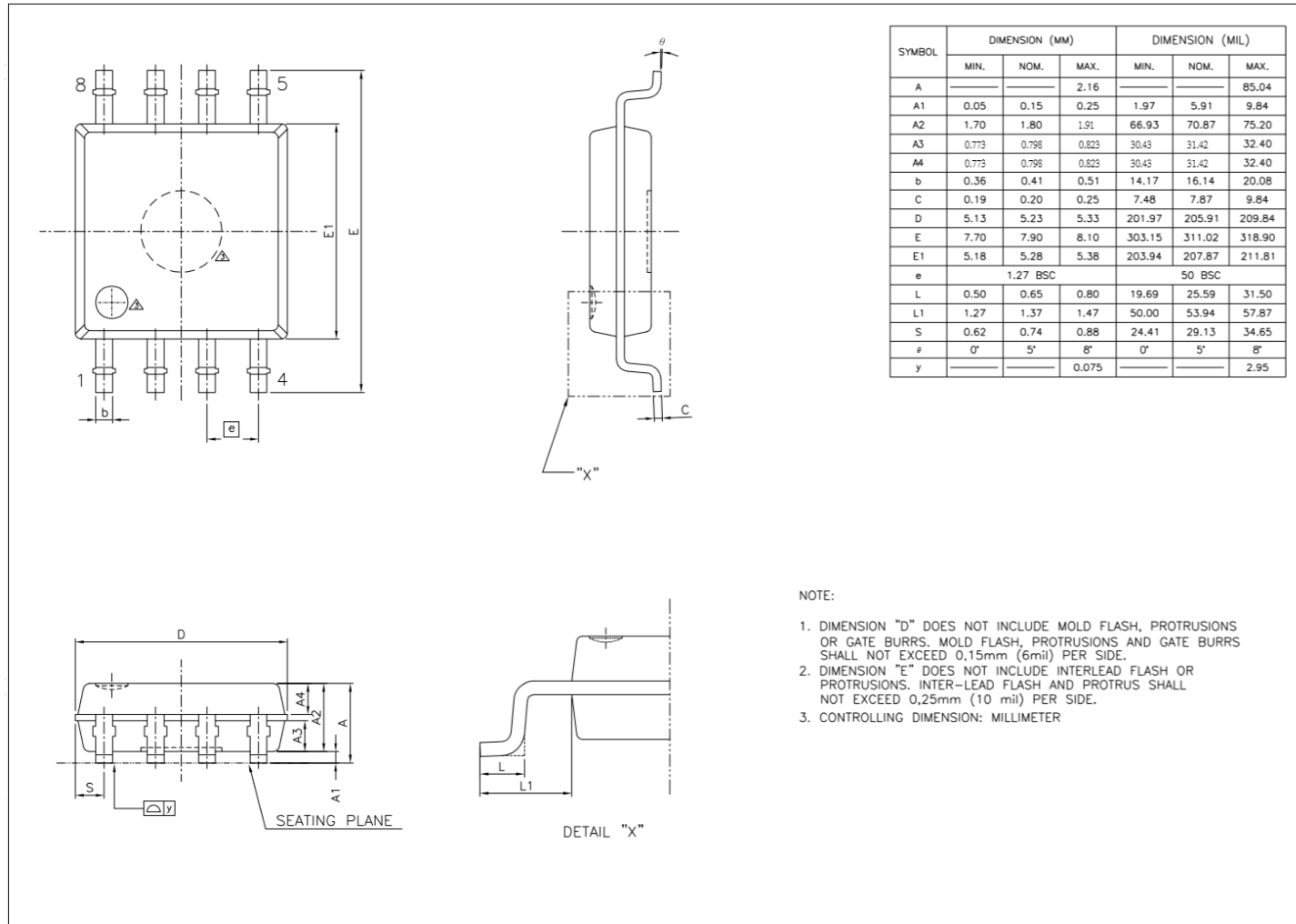
**Figure 4: 8-Pin SOIC**



## Package Drawings

### 8-Pad WSON



**8-Pin SOIC**


## Architecture

ASx016A04 is a high performance serial STT-MRAM device. It features a SPI-compatible bus interface running at 54MHz, eExecute-In-Place (XIP) functionality, and hardware/software based data protection mechanisms.

When CS# is Low, the device is selected and in active power mode. When CS# is High, the device is deselected but can remain in active power mode until ongoing internal operations are completed. Then the device goes into standby power mode and device current consumption drops to I<sub>SB</sub>.

ASx016A04 contains an 8-bit instruction register. All functionality is controlled through the values loaded into this instruction register. In Single SPI mode, the device is accessed via the SI / IO[0] pin. In Dual and Quad SPI modes, IO[0:1] and IO[0:3] are used to access the device respectively. **Table 3** summarizes all the different interface modes supported and their respective I/O usage. **Table 4** shows the clock edge used for each instruction component.

**Nomenclature adoption:** A typical SPI instruction consists of command, address and data components. The bus width to transmit these three components varies based on the SPI interface mode selected. To accurately represent the number of I/Os used to transmit these three components, a nomenclature (command-address-data) is adopted and used throughout this document. Integers placed in the (command-address-data) fields represent the number of I/Os used to transmit the particular component. As an example, 1-1-1 means command, address and data are transmitted on a single I/O (SI / IO[0] or SO / IO[1]). On the other hand, 1-4-4 represents command being sent on a single I/O (SI / IO[0]) and address/data being sent on four I/Os (IO[3:0]).

**Table 3: Interface Modes of Operations**

| Instruction Component | Single SPI<br>(1-1-1) | Dual Input Output SPI<br>(1-1-2) | Dual I/O SPI<br>(1-2-2) | DPI<br>(2-2-2) | Quad Input Output SPI<br>(1-1-4) | Quad I/O SPI<br>(1-4-4) | QPI<br>(4-4-4) |
|-----------------------|-----------------------|----------------------------------|-------------------------|----------------|----------------------------------|-------------------------|----------------|
| Command               | SI / IO[0]            | SI / IO[0]                       | SI / IO[0]              | IO[1:0]        | SI / IO[0]                       | SI / IO[0]              | IO[3:0]        |
| Address               | SI / IO[0]            | SI / IO[0]                       | IO[1:0]                 | IO[1:0]        | SI / IO[0]                       | IO[3:0]                 | IO[3:0]        |
| Data Input            | SI / IO[0]            | IO[1:0]                          | IO[1:0]                 | IO[1:0]        | IO[3:0]                          | IO[3:0]                 | IO[3:0]        |
| Data Output           | SO / IO[1]            | IO[1:0]                          | IO[1:0]                 | IO[1:0]        | IO[3:0]                          | IO[3:0]                 | IO[3:0]        |

**Table 4: Clock Edge Used for instructions in SDR and DDR modes**

| Instruction Type | Command        | Address        | Data Input     | Data Output                 |
|------------------|----------------|----------------|----------------|-----------------------------|
| (1-1-1) SDR      | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>F</sub> <sup>1</sup> |
| (1-1-2) SDR      | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>F</sub> <sup>1</sup> |
| (1-2-2) SDR      | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>F</sub> <sup>1</sup> |
| (2-2-2) SDR      | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>F</sub> <sup>1</sup> |
| (1-1-4) SDR      | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>F</sub> <sup>1</sup> |
| (1-4-4) SDR      | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>F</sub> <sup>1</sup> |
| (4-4-4) SDR      | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>R</sub> | ↕ <sub>F</sub> <sup>1</sup> |

**Notes:**

R: Rising Clock Edge  
 F: Falling Clock Edge

1: Data output from ASx016A04 always begins on the falling edge of the clock.

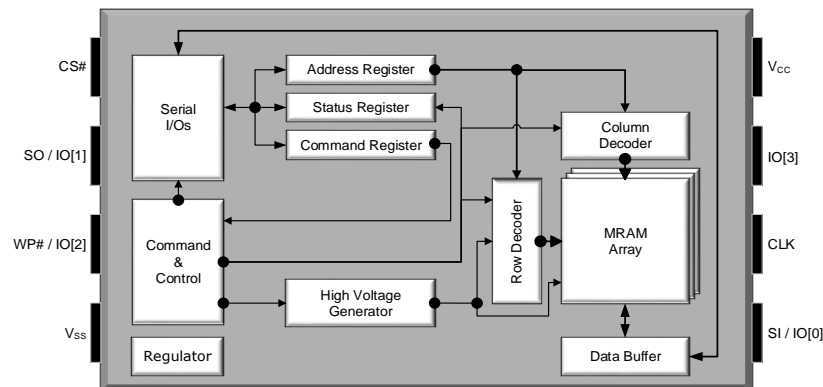
ASx016A04 supports eXecute-In-Place (XIP) which allows completing a series of read and write instructions without having to individually load the read or write command for each instruction. Thus, XIP mode saves command overhead and reduces random read & write access time. A special XIP byte must be entered after the address bits to enable/disable (Axh/Fxh) XIP.

ASx016A04 offers both hardware and software based data protection schemes. Hardware protection is through WP# pin. Software protection is controlled by configuration bits in the Status register. Both schemes inhibit writing to the registers and memory array.

ASx016A04 has a 256-byte Augmented Storage Array which is independent from the main memory array. It is user programmable and can be write protected against inadvertent writes.

Two lower power states are available in ASx016A04, namely Deep Power Down and Hibernate. Data is not lost while the device is in either of these two low power states. Moreover, the device maintains all its configurations.

**Figure 5: Functional Block Diagram**



**Table 5: Modes of Operation**

| Mode            | Current     | CS# | CLK    | SI / IO[3:0]                 | SO / IO[3:0] |
|-----------------|-------------|-----|--------|------------------------------|--------------|
| Standby         | $I_{SB}$    | H   | Gated  | Gated / Hi-Z                 | Hi-Z / Hi-Z  |
| Active - Read   | $I_{READ}$  | L   | Toggle | Command, Address             | Data Output  |
| Active - Write  | $I_{WRITE}$ | L   | Toggle | Command, Address, Data Input | Hi-Z         |
| Deep Power Down | $I_{DPD}$   | H   | Gated  | Gated / Hi-Z                 | Hi-Z / Hi-Z  |
| Hibernate       | $I_{HBN}$   | H   | Gated  | Gated / Hi-Z                 | Hi-Z / Hi-Z  |

**Notes:**

H: High (Logic '1')

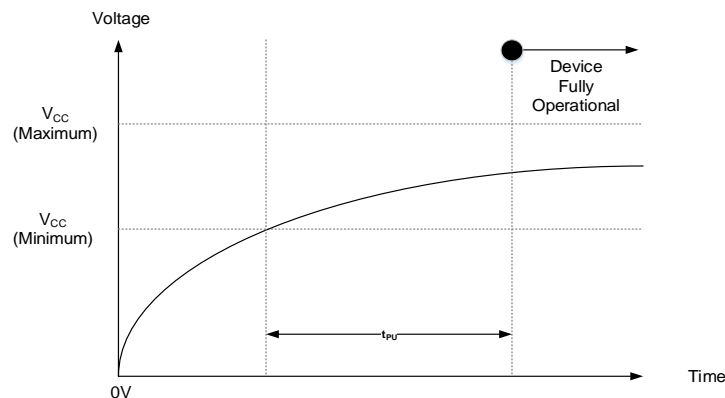
L: Low (Logic '0')

Hi-Z: High Impedance

## Device Initialization

When powering up, the following procedure is required to initialize the device correctly:

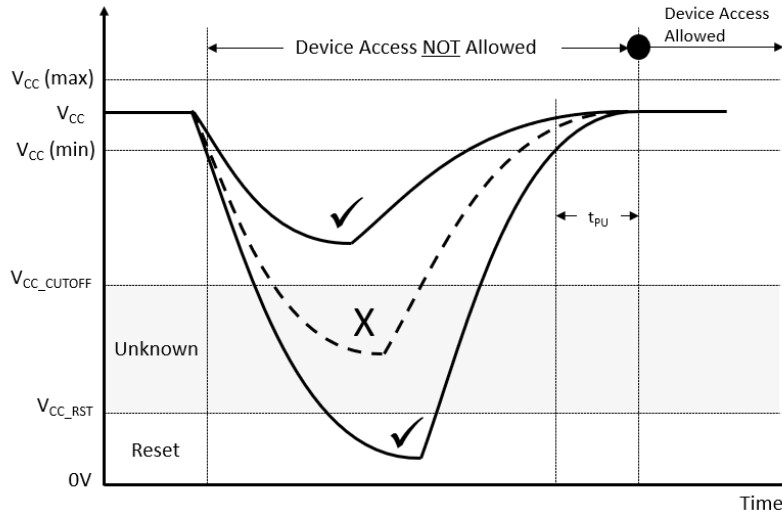
- Ramp up  $V_{CC}$  ( $R_{VR}$ )
- CS# must follow  $V_{CC}$  during power-up (a 10K $\Omega$  pull-up Resistor to  $V_{CC}$  is recommended)
- It is recommended that no instructions are sent to the device when  $V_{CC}$  is below  $V_{CC}$  (minimum)
- During initial power-up, recovering from power loss or brownout, a delay of  $t_{PU}$  is required before normal operation commences
- Upon Power-up, the device is in Standby mode

**Figure 6: Power-Up Behavior**


When powering down or in case of brown-out, the following procedure is required to turn off the device correctly:

- Ramp down  $V_{CC}$  below  $V_{CCRST}$  level
- CS# must follow  $V_{CC}$  during power-down (a 10K $\Omega$  pull-up Resistor to  $V_{CC}$  is recommended)
- The device must not be selected and that no instructions are sent to the device when  $V_{CC}$  is below  $V_{CC}$  (minimum)
- The Power-up timing and device initialization needs to be observed after  $V_{CC}$  ramps up above  $V_{CC}$  (minimum)

- To stabilize the  $V_{CC}$  level, suitable decoupling capacitors close to package  $V_{CC}$  pin is recommended
- Chip functionality not guaranteed if  $V_{CC}$  ramps down between  $V_{CC\_CUTOFF}$  and  $V_{CC\_RST}$  and then ramps up to  $V_{CC}$

**Figure 7: Power-Down and Brown-out Behavior**

**Table 6: Power Up/Down & Voltage Timing – 3.0V**

| Parameter   | Symbol           | Test Conditions                         | 3.0V    |         |         | Units                  |
|---|------------------|---|---------|---------|---------|------------------------|
|   |                  |   | Minimum | Typical | Maximum |                        |
| <b>V<sub>CC</sub> Range</b>                           | $V_{CC}$         | All operating voltages and temperatures | 2.7     | -       | 3.6     | V                      |
| <b>V<sub>CC</sub> Ramp Up Time</b>                    | $R_{VR}$         |   | 30      | -       | -       | $\mu\text{s}/\text{V}$ |
| <b>V<sub>CC</sub> Ramp Down Time</b>                  | $R_{VF}$         |   | 20      | -       | -       | $\mu\text{s}/\text{V}$ |
| <b>V<sub>CC</sub> Power Up to First Instruction</b>   | $t_{PU}$         |   | 250     | -       | -       | $\mu\text{s}$          |
| <b>V<sub>CC</sub> Cutoff – Must Initialize Device</b> | $V_{CC\_CUTOFF}$ |   | 1.6     | -       | -       | V                      |
| <b>V<sub>CC</sub> Reset</b>                           | $V_{CC\_RST}$    |   | 0       | -       | 0.3     | V                      |
| <b>Time to Enter Deep Power Down</b>                  | $t_{EDPD}$       |   | -       | -       | 3       | $\mu\text{s}$          |
| <b>Time to Exit Deep Power Down</b>                   | $t_{EXDPD}$      |   | -       | -       | 400     | $\mu\text{s}$          |
| <b>Time to Enter Hibernate</b>                        | $t_{ENTHIB}$     |   | -       | -       | 3       | $\mu\text{s}$          |
| <b>Time to Exit Hibernate</b>                         | $t_{EXHIB}$      |   | -       | -       | 450     | $\mu\text{s}$          |
| <b>CS# Pulse Width</b>                                | $t_{CSDPD}$      |   | 50      | -       | -       | ns                     |

**Table 7: Power Up/Down & Voltage Timing – 1.8V**

| Parameter   | Symbol                 | Test Conditions                         | 1.8V    |         |         | Units |
|---|------------------------|---|---------|---------|---------|-------|
|   |                        |   | Minimum | Typical | Maximum |       |
| <b>V<sub>CC</sub> Range</b>                           | V <sub>CC</sub>        | All operating voltages and temperatures | 1.71    | -       | 2.0     | V     |
| <b>V<sub>CC</sub> Ramp Up Time</b>                    | R <sub>VR</sub>        |   | 30      | -       | -       | μs/V  |
| <b>V<sub>CC</sub> Ramp Down Time</b>                  | R <sub>VF</sub>        |   | 20      | -       | -       | μs/V  |
| <b>V<sub>CC</sub> Power Up to First Instruction</b>   | t <sub>PU</sub>        |   | 250     | -       | -       | μs    |
| <b>V<sub>CC</sub> Cutoff – Must Initialize Device</b> | V <sub>CC-CUTOFF</sub> |   | 1.6     | -       | -       | V     |
| <b>V<sub>CC</sub> Reset</b>                           | V <sub>CC-RST</sub>    |   | 0       | -       | 0.2     | V     |
| <b>Time to Enter Deep Power Down</b>                  | t <sub>EDPD</sub>      |   | -       | -       | 3       | μs    |
| <b>Time to Exit Deep Power Down</b>                   | t <sub>EXDPD</sub>     |   | -       | -       | 400     | μs    |
| <b>Time to Enter Hibernate</b>                        | t <sub>ENTHIB</sub>    |   | -       | -       | 3       | μs    |
| <b>Time to Exit Hibernate</b>                         | t <sub>EXHIB</sub>     |   | -       | -       | 450     | μs    |
| <b>CS# Pulse Width</b>                                | t <sub>CSDPD</sub>     |   | 50      | -       | -       | ns    |



## Memory Map

**Table 8: Memory Map**

| Density     | Address Range      | 24-bit Address [23:0] |                      |
|-------------|--------------------|-----------------------|----------------------|
| <b>1Mb</b>  | 000000h – 01FFFFh  | [23:17] – Logic '0'   | [16:0] - Addressable |
| <b>4Mb</b>  | 000000h – 07FFFFh  | [23:19] – Logic '0'   | [18:0] - Addressable |
| <b>8Mb</b>  | 000000h – 0FFFFFFh | [23:20] – Logic '0'   | [19:0] - Addressable |
| <b>16Mb</b> | 000000h – 1FFFFFFh | [23:21] – Logic '0'   | [20:0] - Addressable |

## Augmented Storage Array Map

**Table 9: Augmented Storage Array Map**

| Density     | Address Range                  | 24-bit Address [23:0] |                     |
|-------------|--------------------------------|-----------------------|---------------------|
| <b>1Mb</b>  | 000000h – 0000FFh <sup>1</sup> | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>4Mb</b>  | 000000h – 0000FFh <sup>1</sup> | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>8Mb</b>  | 000000h – 0000FFh <sup>1</sup> | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>16Mb</b> | 000000h – 0000FFh <sup>1</sup> | [23:8] – Logic '0'    | [7:0] - Addressable |

**Notes:**

1: The 256-byte augmented storage array is divided into 8 individually readable and writeable sections (32 bytes per section). After an individual section is programmed, it can be write protected to prevent further programming.

**Table 10: Individual Section Address Range**

| Section  | Address Range     | 24-bit Address [23:0] |                     |
|----------|-------------------|-----------------------|---------------------|
| <b>0</b> | 000000h – 00001Fh | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>1</b> | 000020h – 00003Fh | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>2</b> | 000040h – 00005Fh | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>3</b> | 000060h – 00007Fh | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>4</b> | 000080h – 00009Fh | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>5</b> | 0000A0h – 0000BFh | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>6</b> | 0000C0h – 0000DFh | [23:8] – Logic '0'    | [7:0] - Addressable |
| <b>7</b> | 0000E0h – 0000FFh | [23:8] – Logic '0'    | [7:0] - Addressable |

## Register Addresses

*Table 11: Register Addresses*

| <b>Register Name</b>                  | <b>Address</b> |
|---------------------------------------|----------------|
| <b>Status Register</b>                | 0x000000h      |
| <b>Configuration Register 1</b>       | 0x000002h      |
| <b>Configuration Register 2</b>       | 0x000003h      |
| <b>Configuration Register 3</b>       | 0x000004h      |
| <b>Configuration Register 4</b>       | 0x000005h      |
| <b>Device Identification Register</b> | 0x000030h      |
| <b>Unique Identification Register</b> | 0x000040h      |

**Notes:**

1: Register address space is different from the memory array and augmented storage array.

2: The Status and Configuration registers need to be re-initialized after a solder reflow process. Refer to application note AN000008 for the detailed description.

## Register Map

### Status Register / Device Protection Register (Read/Write)

Status register is a legacy SPI register and contains options for enabling/disabling data protection.

**Table 12: Status Register – Read and Write**

| Bits  | Name     | Description   | Read / Write | Default State | Selection Options  |
|-------|----------|---|--------------|---------------|--|
| SR[7] | WP#EN    | Hardware Based WP# Protection Enable/Disable          | R/W          | 0             | 1: Protection Enabled – write protects when WP# is Low<br>0: Protection Disabled – Doesn't write protect when WP# is Low |
| SR[6] | SNPEN    | Serial Number Protection Enable/Disable               | R/W          | 0             | 1: S/N Write protected - protection enabled<br>0: S/N Writable - protection disabled                                     |
| SR[5] | TBSEL    | Software Top/Bottom Memory Array Protection Selection | R/W          | 0             | 1: Bottom Protection Enabled (Lower Address Range)<br>0: Top Protection Enabled (Higher Address Range)                   |
| SR[4] | BPSEL[2] | Block Protect Selection Bit 2                         | R/W          | 0             | Block Protection Bits (Table 13, <b>Table 14</b> )   |
| SR[3] | BPSEL[1] | Block Protect Selection Bit 1                         | R/W          | 0             |  |
| SR[2] | BPSEL[0] | Block Protect Selection Bit 0                         | R/W          | 0             |  |
| SR[1] | WREN     | Write Operation Protection Enable/Disable             | R            | 0             | 1: Write Operation Protection Disabled<br>0: Write Operation Protection Enabled  |
| SR[0] | RSVD     | Reserved  | R            | 0             | Reserved for future use  |

**Table 13: Top Block Protection Address Range Selection (TBSEL=0)**

| BPSEL [2] | BPSEL [1] | BPSEL [0] | Protected Portion | 1Mb               | 4Mb               | 8Mb                | 16Mb               |
|-----------|-----------|-----------|-------------------|-------------------|-------------------|--------------------|--------------------|
| 0         | 0         | 0         | None              | None              | None              | None               | None               |
| 0         | 0         | 1         | Upper 1/64        | 01F800h – 01FFFFh | 07E000h – 07FFFFh | 0FC000h – 0FFFFFFh | 1F8000h – 1FFFFFFh |
| 0         | 1         | 0         | Upper 1/32        | 01F000h – 01FFFFh | 07C000h – 07FFFFh | 0F8000h – 0FFFFFFh | 1F0000h – 1FFFFFFh |
| 0         | 1         | 1         | Upper 1/16        | 01E000h – 01FFFFh | 078000h – 07FFFFh | 0F0000h – 0FFFFFFh | 1E0000h – 1FFFFFFh |
| 1         | 0         | 0         | Upper 1/8         | 01C000h – 01FFFFh | 070000h – 07FFFFh | 0E0000h – 0FFFFFFh | 1C0000h – 1FFFFFFh |
| 1         | 0         | 1         | Upper 1/4         | 018000h – 01FFFFh | 060000h – 07FFFFh | 0C0000h – 0FFFFFFh | 180000h – 1FFFFFFh |
| 1         | 1         | 0         | Upper 1/2         | 010000h – 01FFFFh | 040000h – 07FFFFh | 080000h – 0FFFFFFh | 1F0000h – 1FFFFFFh |
| 1         | 1         | 1         | All               | 000000h – 01FFFFh | 000000h – 07FFFFh | 000000h – 0FFFFFFh | 000000h – 1FFFFFFh |

**Table 14: Bottom Block Protection Address Range Selection (TBPSEL=1)**

| BPSEL [2] | BPSEL [1] | BPSEL [0] | Protected Portion | 1Mb               | 4Mb               | 8Mb                | 16Mb               |
|-----------|-----------|-----------|-------------------|-------------------|-------------------|--------------------|--------------------|
| 0         | 0         | 0         | None              | None              | None              | None               | None               |
| 0         | 0         | 1         | Lower 1/64        | 000000h – 0007FFh | 000000h – 001FFFh | 000000h – 003FFFh  | 000000h – 007FFFh  |
| 0         | 1         | 0         | Lower 1/32        | 000000h – 00FFFFh | 000000h – 003FFFh | 000000h – 007FFFh  | 000000h – 00FFFFh  |
| 0         | 1         | 1         | Lower 1/16        | 000000h – 001FFFh | 000000h – 007FFFh | 000000h – 00FFFFh  | 000000h – 01FFFFh  |
| 1         | 0         | 0         | Lower 1/8         | 000000h – 003FFFh | 000000h – 00FFFFh | 000000h – 01FFFFh  | 000000h – 03FFFFh  |
| 1         | 0         | 1         | Lower 1/4         | 000000h – 007FFFh | 000000h – 01FFFFh | 000000h – 03FFFFh  | 000000h – 07FFFFh  |
| 1         | 1         | 0         | Lower 1/2         | 000000h – 00FFFFh | 000000h – 03FFFFh | 000000h – 07FFFFh  | 000000h – 0FFFFFFh |
| 1         | 1         | 1         | All               | 000000h – 01FFFFh | 000000h – 07FFFFh | 000000h – 0FFFFFFh | 000000h – 1FFFFFFh |

**Table 15: Write Protection Modes**

| WREN (Status Register) | WP#EN (Status Register) | WP# (Pin) | Status & Configuration Registers | Memory <sup>1</sup> Array Protected Area | Memory <sup>1</sup> Array Unprotected Area |
|------------------------|-------------------------|-----------|----------------------------------|--|--|
| 0                      | X                       | X         | Protected                        | Protected                                | Protected                                  |
| 1                      | 0                       | X         | Unprotected                      | Protected                                | Unprotected                                |
| 1                      | 1                       | Low       | Protected                        | Protected                                | Unprotected                                |
| 1                      | 1                       | High      | Unprotected                      | Protected                                | Unprotected                                |

**Notes:**

High: Logic '1'

Low: Logic '0'

X: Don't Care – Can be Logic '0' or '1'

Protected: Write protected

Unprotected: Writable

1: Memory address range protection based on Block Protection Bits

**Augmented Storage Array Protection Register (Read/Write)**

Augmented Storage Array Protection register contains options for enabling/disabling data protection for eight 32-byte sections.

**Table 16: Augmented Storage Array Protection Register – Read and Write**

| Bits   | Name    | Description                                   | Read / Write | Default State | Selection Options                               |
|--------|---------|---|--------------|---------------|---|
| ASP[7] | ASPS[7] | ASA Section 7 Write Protection Enable/Disable | R/W          | 0             | 1: Protection Enabled<br>0: Protection Disabled |
| ASP[6] | ASPS[6] | ASA Section 6 Write Protection Enable/Disable | R/W          | 0             | 1: Protection Enabled<br>0: Protection Disabled |
| ASP[5] | ASPS[5] | ASA Section 5 Write Protection Enable/Disable | R/W          | 0             | 1: Protection Enabled<br>0: Protection Disabled |
| ASP[4] | ASPS[4] | ASA Section 4 Write Protection Enable/Disable | R/W          | 0             | 1: Protection Enabled<br>0: Protection Disabled |
| ASP[3] | ASPS[3] | ASA Section 3 Write Protection Enable/Disable | R/W          | 0             | 1: Protection Enabled<br>0: Protection Disabled |
| ASP[2] | ASPS[2] | ASA Section 2 Write Protection Enable/Disable | R/W          | 0             | 1: Protection Enabled<br>0: Protection Disabled |
| ASP[1] | ASPS[1] | ASA Section 1 Write Protection Enable/Disable | R/W          | 0             | 1: Protection Enabled<br>0: Protection Disabled |
| ASP[0] | ASPS[0] | ASA Section 0 Write Protection Enable/Disable | R/W          | 0             | 1: Protection Enabled<br>0: Protection Disabled |

### Device Identification Register (Read Only)

Device identification register contains Avalanche’s Manufacturing ID along with device configuration information.

**Table 17: Device Identification Register – Read Only**

| Bits     | Avalanche Manufacturer's ID | Device Configuration |           |           |          |         |
|----------|-----------------------------|----------------------|-----------|-----------|----------|---------|
|          |                             | Interface            | Voltage   | Temp      | Density  | Freq    |
| ID[31:0] | ID[31:24]                   | ID[23:20]            | ID[19:16] | ID[15:12] | ID[11:8] | ID[7:0] |

| Manufacturer ID | Interface    | Voltage     | Temperature        | Density     | Frequency        |
|-----------------|--------------|-------------|--------------------|-------------|------------------|
| 31-24           | 23-20        | 19-16       | 15-12              | 11-8        | 7-0              |
| 1110 0110       | 0000-HP QSPI | 0001 - 3V   | 0010 - -40°C-125°C | 0101 - 16Mb | 00000010 - 54MHz |
|                 |              | 0010 - 1.8V |                    |             |                  |

## Serial Number Register (Read/Write)

Serial Number register is user writable.

**Table 18: Serial Number Register – Read and Write**

| Bits            | Name | Description         | Read / Write | Default State <sup>1</sup> | Selection Options                     |
|-----------------|------|---------------------|--------------|----------------------------|---------------------------------------|
| <b>SN[63:0]</b> | SN   | Serial Number Value | R/W          | 000000000000<br>0000h      | Value stored is based on the customer |

**Notes:**

1: The default value is how the device is shipped from the factory.

## Unique Identification Register (Read Only)

Unique Identification register contains a number unique to every device.

**Table 19: Unique ID Register – Read Only**

| Bits             | Name | Description                        | Read / Write | Selection Options   |
|------------------|------|------------------------------------|--------------|---|
| <b>UID[63:0]</b> | UID  | Unique Identification Number Value | R            | Value stored is written in the factory and is device specific |

### Configuration Register 1 (Read/Write)

Configuration Register 1 controls locking/unlocking data protection options set in the Status register. Once locked, the protection options cannot be changed in the Status register.

**Table 20: Configuration Register 1 – Read and Write**

| Bits   | Name  | Description   | Read / Write | Default State | Selection Options  |
|--------|-------|---|--------------|---------------|--|
| CR1[7] | RSVD  | Reserved  | R            | 0             | Reserved for future use  |
| CR1[6] | RSVD  | Reserved  | R            | 0             | Reserved for future use  |
| CR1[5] | RSVD  | Reserved  | R            | 0             | Reserved for future use  |
| CR1[4] | RSVD  | Reserved  | R            | 0             | Reserved for future use  |
| CR1[3] | RSVD  | Reserved  | R            | 0             | Reserved for future use  |
| CR1[2] | MAPLK | Status Register Lock Enable/Disable (TBSEL, BPSEL[2:0]) | R/W          | 0             | 1: Lock TBSEL and BPSEL[2:0]<br>0: Unlock TBSEL and BPSEL[2:0]                           |
| CR1[1] | RSVD  | Reserved  | R            | 0             | Reserved for future use  |
| CR1[0] | ASPLK | Augmented Storage Array Data Protection                 | R/W          | 0             | 1: Write Protect Augmented Storage Array<br>0: Not Write Protect Augmented Storage Array |

### Configuration Register 2 (Read/Write)

Configuration Register 2 controls the interface type along with memory array access latency.

**Table 21: Configuration Register 2 – Read and Write**

| Bits   | Name     | Description  | Read / Write   | Default State | Selection Options   |
|--------|----------|--|----------------|---------------|---|
| CR2[7] | RSVD     | Reserved   | R              | 0             | Reserved for future use   |
| CR2[6] | QPISL    | Quad SPI (QPI 4-4-4) Interface Mode Enable/Disable | R <sup>2</sup> | 0             | 1: Quad SPI (QPI 4-4-4) Enabled<br>0: Single SPI (SPI 1-1-1) Enabled  |
| CR2[5] | RSVD     | Reserved   | R              | 0             | Reserved for future use   |
| CR2[4] | DPISL    | Dual SPI (DPI 2-2-2) Interface Mode Enable/Disable | R <sup>2</sup> | 0             | 1: Dual SPI (DPI 2-2-2) Enabled<br>0: Single SPI (SPI 1-1-1) Enabled  |
| CR2[3] | MLATS[3] | Memory Array Read Latency Selection <sup>1</sup>   | R/W            | 0             | 0000: 0 Cycles - Default<br>0001: 1 Cycle<br>0010: 2 Cycles<br>0011: 3 Cycles<br>0100: 4 Cycles<br>0101: 5 Cycles |
| CR2[2] | MLATS[2] |  |                | 0             |   |

| Bits   | Name     | Description | Read / Write | Default State | Selection Options   |
|--------|----------|-------------|--------------|---------------|---|
| CR2[1] | MLATS[1] |             |              | 0             | 0110: 6 Cycles<br>0111: 7 Cycles<br>1000: 8 Cycles<br>1001: 9 Cycle<br>1010: 10 Cycles<br>1011: 11 Cycles<br>1100: 12 Cycles<br>1101: 13 Cycles<br>1110: 14 Cycles<br>1111: 15 Cycles |
| CR2[0] | MLATS[0] |             |              | 0             |   |

**Notes:**

- 1: Latency is frequency dependent. Please consult **Table 22** and **Table 23**.
- 2: These interface options can only be set through instructions.

**Table 22: Memory Array Read Latency Cycles vs. Maximum Clock Frequency (with XIP)**

| Read Type   | Latency | Max Frequency |
|-------------|---------|---------------|
|             |         | ASxxxx2x054xx |
| (1-1-1) SDR | 8-15    | 54MHz         |
| (1-1-2) SDR |         | 54MHz         |
| (1-2-2) SDR |         | 54MHz         |
| (2-2-2) SDR |         | 54MHz         |
| (1-1-4) SDR | 12-15   | 54MHz         |
| (1-4-4) SDR |         | 54MHz         |
| (4-4-4) SDR |         | 54MHz         |

**Table 23: Memory Read Latency Cycles vs. Maximum Clock Frequency (without XIP)**

| Read Type   | Latency | Max Frequency |
|-------------|---------|---------------|
|             |         | ASxxxx2x054xx |
| (1-1-1) SDR | 8-15    | 54MHz         |
| (2-2-2) SDR | 8-15    | 54MHz         |
| (4-4-4) SDR | 8-15    | 54MHz         |

**Table 24: Augmented Storage Array Read Latency Cycles vs. Maximum Clock Frequency**

| Read Type   | Latency | Max Frequency |
|-------------|---------|---------------|
|             |         | ASxxxx2x054xx |
| (1-1-1) SDR | 8-15    | 40MHz         |



**Table 25: Read Any Register Command Latency Cycles vs. Maximum Clock Frequency**

| Read Type   | Max Frequency | Latency Cycles |
|-------------|---------------|----------------|
| (1-1-1) SDR | 54MHz         | 8              |
| (2-2-2) SDR | 54MHz         | 4              |
| (4-4-4) SDR | 54MHz         | 2              |

### Configuration Register 3 (Read/Write)

Configuration Register 3 controls the output driver strength along with read data wrap selection.

**Table 26: Configuration Register 3 – Read and Write**

| Bits   | Name     | Description                       | Read / Write | Default  |  | Selection Options  |
|--------|----------|-----------------------------------|--------------|--|--|--|
|        |          |                                   |              | 1.8V   | 3.0V   |  |
| CR3[7] | ODSEL[2] | Output Driver Strength Selector   | R/W          | 0  | 0  | 1.8V 3.0V<br>000: 45Ω <sup>1</sup> 35Ω<br>001: 120Ω 75Ω<br>010: 90Ω 60Ω<br>011: 70Ω 45Ω <sup>1</sup><br>100: 45Ω 35Ω<br>101: 60Ω 40Ω<br>110: 30Ω 20Ω<br>111: 20Ω 15Ω |
| CR3[6] | ODSEL[1] |                                   |              | 0  | 1  |  |
| CR3[5] | ODSEL[0] |                                   |              | 0  | 1  |  |
| CR3[4] | WRAPS    |                                   |              | Read WRAP Enable / Disable (16/32/64/128/256 Byte) | R/W  | 0  |
| CR3[3] | RSVD     | Reserved                          | R            | 0  | Reserved for future use  |  |
| CR3[2] | WRPLS[2] | Wrap Length Selector <sup>2</sup> | R/W          | 0  | 000: 16-byte Boundary<br>001: 32-byte Boundary<br>010: 64-byte Boundary<br>011: 128-byte Boundary<br>100: 256-byte Boundary<br>101: Reserved<br>110: Reserved<br>111: Reserved |  |
| CR3[1] | WRPLS[1] |                                   |              | 0  |  |  |
| CR3[0] | WRPLS[0] |                                   |              | 0  |  |  |

**Notes:**

1: Default Setting ( $V_{CC}$  dependent).

2: If Wrap is enabled, the read data wraps within an aligned 16/32/64/128/256-byte boundary at any address. The starting address entered selects the group of bytes and the first data returned is the addressed byte. Bytes are then read sequentially until the end of the group boundary is reached. If read continues, the address wraps to the beginning of the group and continues to read sequentially.

## Configuration Register 4 (Read/Write)

Configuration Register 4 controls Write Enable protection (WREN – Status Register) reset functionality during memory array writing<sup>1</sup>. This functionality makes SPI MRAM compatible to other SPI devices.

**Table 27: Configuration Register 4 – Read and Write**

| Bits   | Name     | Description  | Read / Write | Default State | Selection Options   |
|--------|----------|--|--------------|---------------|---|
| CR4[7] | RSVD     | Reserved   | R/W          | 0             | Reserved for future use   |
| CR4[6] | RSVD     | Reserved   |              | 0             | Reserved for future use   |
| CR4[5] | RSVD     | Reserved   |              | 0             | Reserved for future use   |
| CR4[4] | RSVD     | Reserved   |              | 0             | Reserved for future use   |
| CR4[3] | RSVD     | Reserved   |              | 0             | Reserved for future use   |
| CR4[2] | RSVD     | Reserved   |              | 1             | Reserved <sup>2</sup>   |
| CR4[1] | WRENS[1] | WREN Reset Selector                                    |              | 0             | 00: Normal: WREN is prerequisite to all Memory Array Write instruction. (WREN is reset after CS# goes High)<br>01: SRAM: WREN is not a prerequisite to Memory Array Write instruction (WREN is ignored)                             |
| CR4[0] | WRENS[0] | (Memory & Augmented Storage Array Write Functionality) |              | 1             | 10: Back-to-Back: WREN is prerequisite to only the first Memory Array Write instruction. WREN disable instruction must be executed to reset WREN. (WREN does not reset once CS# goes High)<br>11: Illegal - Reserved for future use |

**Notes:**

1: Write Enable protection (WREN – Status Register) for Registers is maintained irrespective of the Configuration Register 4 settings. In other words, all register write instructions require WREN to be set and WREN resets once CS# goes High for the write instruction.

2: Must be set to “1”. Writing a “0” to this bit may impact device functionality.

## Instruction Set

**Table 28: Instruction Set**

| #  | Instruction Name      | Command (Opcode) | (1-0-0) | (1-0-1) | (1-1-1) | (1-1-2) | (1-2-2) | (2-0-0) | (2-0-2) | (2-2-2) | (1-1-4) | (1-4-4) | (4-0-0) | (4-0-4) | (4-4-4) | XIP | SDR | Latency Cycles | Data Bytes | Max. Frequency      | Prerequisite |
|----|-----------------------|------------------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|-----|-----|----------------|------------|---------------------|--------------|
| 1  | No Operation          | NOOP<br>00h      | •       |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              |              |
| 2  | Write Enable          | WREN<br>06h      | •       |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              |              |
| 3  | Write Disable         | WRDI<br>04h      | •       |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              |              |
| 4  | Enable DPI            | DPIE<br>37h      | •       |         |         |         |         |         |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              |              |
| 5  | Enable QPI            | QPIE<br>38h      | •       |         |         |         |         | •       |         |         |         |         |         |         |         |     | •   |                |            | 54 MHz              |              |
| 6  | Enable SPI            | SPIE<br>FFh      |         |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              |              |
| 7  | Enter Deep Power Down | DPDE<br>B9h      | •       |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              |              |
| 8  | Enter Hibernate       | HBNE<br>BAh      | •       |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              |              |
| 9  | Software Reset Enable | SRTE<br>66h      | •       |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              |              |
| 10 | Software Reset        | SRST<br>99h      | •       |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 MHz              | SRTE         |
| 11 | Exit Deep Power Down  | DPDX<br>ABh      | •       |         |         |         |         | •       |         |         |         |         | •       |         |         |     | •   |                |            | 54 <sup>7</sup> MHz |              |
| 12 | Read Status Register  | RDSR<br>05h      |         | •       |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 1          | 54 MHz              |              |

| #  | Instruction Name                         | Command (Opcode) | (1-0-0) | (1-0-1) | (1-1-1) | (1-1-2) | (1-2-2) | (2-0-0) | (2-0-2) | (2-2-2) | (1-1-4) | (1-4-4) | (4-0-0) | (4-0-4) | (4-4-4) | XIP | SDR | Latency Cycles | Data Bytes | Max. Frequency | Prerequisite |
|----|--|------------------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|-----|-----|----------------|------------|----------------|--------------|
| 13 | Read Configuration Register 1            | RDC1<br>35h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 1          | 54 MHz         |              |
| 14 | Read Configuration Register 2            | RDC2<br>3Fh      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 1          | 54 MHz         |              |
| 15 | Read Configuration Register 3            | RDC3<br>44h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 1          | 54 MHz         |              |
| 16 | Read Configuration Register 4            | RDC4<br>45h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 1          | 54 MHz         |              |
| 17 | Read Configuration Register 1, 2, 3, 4   | RDCX<br>46h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 4          | 54 MHz         |              |
| 18 | Read Device ID                           | RDID<br>9Fh      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 4          | 54 MHz         |              |
| 19 | Read Unique ID                           | RUID<br>4Ch      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 8          | 54 MHz         |              |
| 20 | Read Serial Number Register              | RDSN<br>C3h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 8          | 54 MHz         |              |
| 21 | Read Augmented Array Protection Register | RDAP<br>14h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 1          | 54 MHz         |              |
| 22 | Read Any Register - Address Based        | RDAR<br>65h      |         |         | •       |         |         |         |         | •       |         |         |         |         | •       |     | •   | •              | 1 to 8     | 54 MHz         |              |
| 23 | Write Status Register                    | WRSR<br>01h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 1          | 54 MHz         | WREN         |
| 24 | Write Configuration Registers 1, 2, 3, 4 | WRCX<br>87h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 4          | 54 MHz         | WREN         |
| 25 | Write Serial Number Register             | WRSN<br>C2h      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 8          | 54 MHz         | WREN         |

| #  | Instruction Name                          | Command (Opcode) | (1-0-0) | (1-0-1) | (1-1-1) | (1-1-2) | (1-2-2) | (2-0-0) | (2-0-2) | (2-2-2) | (1-1-4) | (1-4-4) | (4-0-0) | (4-0-4) | (4-4-4) | XIP | SDR | Latency Cycles | Data Bytes | Max. Frequency | Prerequisite |
|----|---|------------------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|-----|-----|----------------|------------|----------------|--------------|
| 26 | Write Augmented Array Protection Register | WRAP<br>1Ah      | •       |         |         |         |         |         | •       |         |         |         |         | •       |         |     | •   |                | 1          | 54 MHz         | WREN         |
| 27 | Write Any Register - Address Based        | WRAR<br>71h      |         |         | •       |         |         |         |         | •       |         |         |         |         | •       |     | •   |                | 1 to 8     | 54 MHz         | WREN         |
| 28 | Read Memory Array - SDR                   | READ<br>03h      |         |         | •       |         |         |         |         |         |         |         |         |         |         |     | •   |                | 1 to ∞     | 50 MHz         |              |
| 29 | Fast Read Memory Array - SDR              | RDFT<br>0Bh      |         |         | •       |         |         |         |         | •       |         |         |         |         | •       | •   | •   | •              | 1 to ∞     | 54 MHz         |              |
| 30 | Read Dual Output Memory Array - SDR       | RDDO<br>3Bh      |         |         |         | •       |         |         |         |         |         |         |         |         |         | •   | •   | •              | 1 to ∞     | 54 MHz         |              |
| 31 | Read Quad Output Memory Array - SDR       | RDQO<br>6Bh      |         |         |         |         |         |         |         |         | •       |         |         |         |         | •   | •   | •              | 1 to ∞     | 54 MHz         |              |
| 32 | Read Dual I/O Memory Read - SDR           | RDDI<br>BBh      |         |         |         |         | •       |         |         |         |         |         |         |         |         | •   | •   | •              | 1 to ∞     | 54 MHz         |              |
| 33 | Read Quad I/O Memory Read - SDR           | RDQI<br>EBh      |         |         |         |         |         |         |         |         |         | •       |         |         |         | •   | •   | •              | 1 to ∞     | 54 MHz         |              |
| 34 | Write Memory Array - SDR                  | WRTE<br>02h      |         |         | •       |         |         |         |         |         |         |         |         |         |         |     | •   |                | 1 to ∞     | 54 MHz         | WREN         |
| 35 | Fast Write Memory Array - SDR             | WRFT<br>DAh      |         |         | •       |         |         |         |         | •       |         |         |         |         | •       | •   | •   |                | 1 to ∞     | 54 MHz         | WREN         |
| 36 | Write Dual Input Memory Array - SDR       | WDUI<br>A2h      |         |         |         | •       |         |         |         |         |         |         |         |         |         | •   | •   |                | 1 to ∞     | 54 MHz         | WREN         |
| 37 | Write Quad Input Memory Array - SDR       | WQDI<br>32h      |         |         |         |         |         |         |         |         | •       |         |         |         |         | •   | •   |                | 1 to ∞     | 54 MHz         | WREN         |
| 38 | Write Dual I/O Memory Array - SDR         | WDIO<br>A1h      |         |         |         |         | •       |         |         |         |         |         |         |         |         | •   | •   |                | 1 to ∞     | 54 MHz         | WREN         |

## 16Mbit SPI (4-4-4) Space-Grade MRAM Memory

| #  | Instruction Name                    | Command (Opcode) | (1-0-0) | (1-0-1) | (1-1-1) | (1-1-2) | (1-2-2) | (2-0-0) | (2-0-2) | (2-2-2) | (1-1-4) | (1-4-4) | (4-0-0) | (4-0-4) | (4-4-4) | XIP | SDR | Latency Cycles | Data Bytes | Max. Frequency | Prerequisite |
|----|-------------------------------------|------------------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|---------|-----|-----|----------------|------------|----------------|--------------|
| 39 | Write Quad I/O Memory Array - SDR   | WQIO<br>D2h      |         |         |         |         |         |         |         |         |         | •       |         |         |         | •   | •   |                | 1 to ∞     | 54 MHz         | WREN         |
| 40 | Read Augmented Storage Array - SDR  | RDAS<br>4Bh      |         |         | •       |         |         |         |         |         |         |         |         |         |         |     | •   | •              | 1 to 256   | 50 MHz         |              |
| 41 | Write Augmented Storage Array - SDR | WRAS<br>42h      |         |         | •       |         |         |         |         |         |         |         |         |         |         |     | •   |                | 1 to 256   | 54 MHz         | WREN         |

**Notes:**

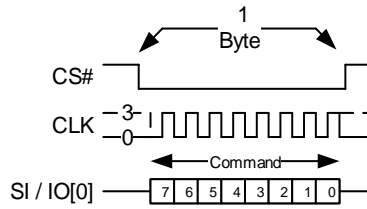
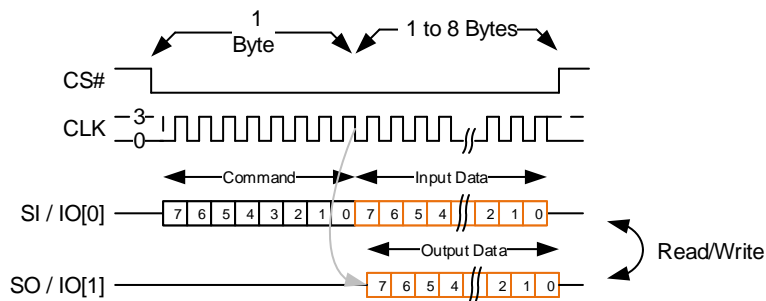
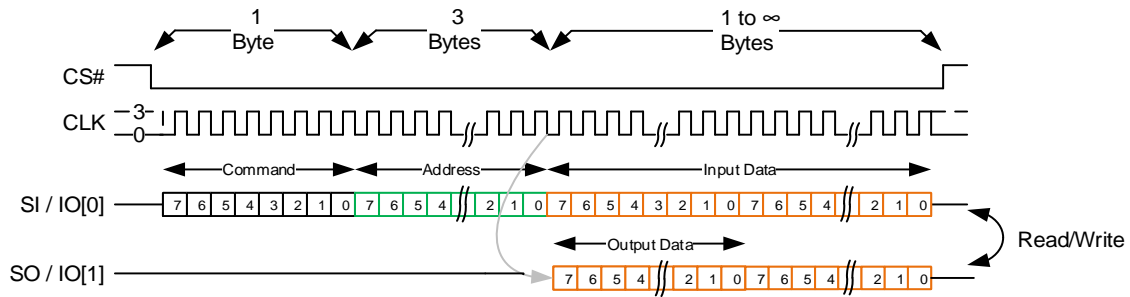
- 1: A typical SPI instruction consists of command, address and data components. The bus width to transmit these three components varies based on the SPI interface mode selected. To accurately represent the number of I/Os used to transmit these three components, a nomenclature (command-address-data) is adopted and used throughout this document. Integers placed in the (command-address-data) fields represent the number of I/Os used to transmit the particular component. As an example, 1-1-1 means command, address and data are transmitted on a single I/O (SI / IO[0] or SO / IO[1]). On the other hand, 1-4-4 represents command being sent on a single I/O (SI / IO[0]) and address/data being sent on four I/Os (IO[3:0]).
- 2: XIP allows completing a series of read and write instructions without having to individually load the read or write command for each instruction. A special mode byte must be entered after the address bits to enable/disable XIP – Axh / Fxh.
- 3: Read instruction must include Latency cycles to meet higher frequency. They are configurable (Configuration Register 2 – CR2[3:0]) and frequency dependent.
- 4: The augmented storage array is 256-Bytes in size. The address bits ADDR[23:8] must be Logic '0' for this instruction.
- 5: Registers do not wrap data during reads. Reading beyond the specified number of bytes will yield indeterminate data.
- 6: WREN prerequisite for array writing is configurable (Configuration Register 4 – CR4[1:0]).
- 7: For the Exit Deep Power Down command, the maximum frequency is 54MHz for 1-1-1 operation and 36MHz for 2-2-2 and 4-4-4 operations.

## Instruction Description and Structures

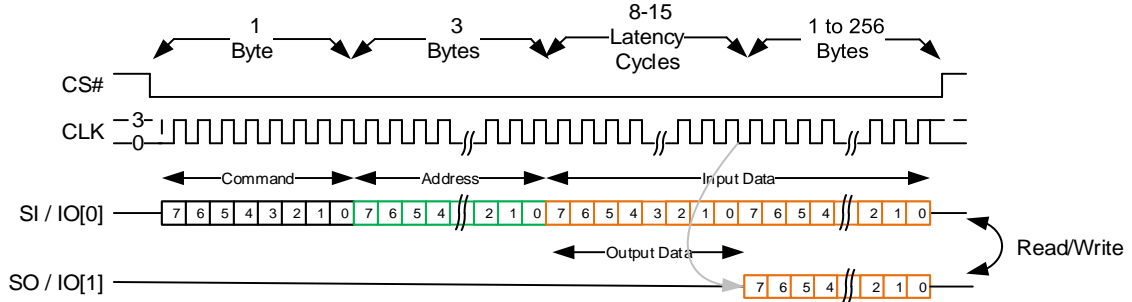
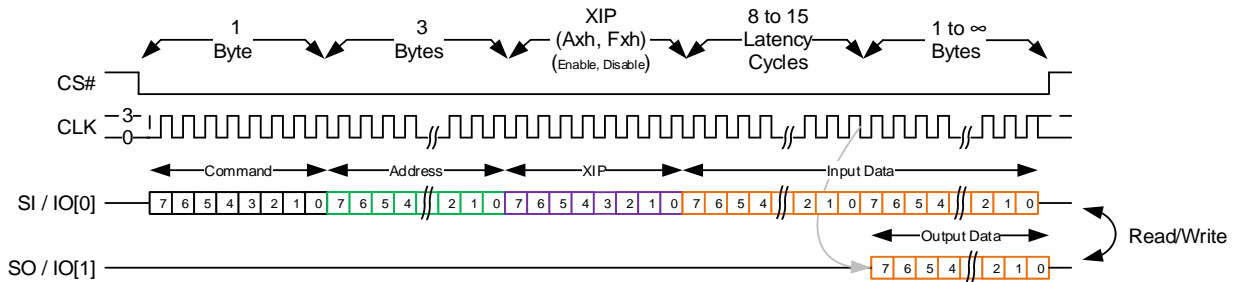
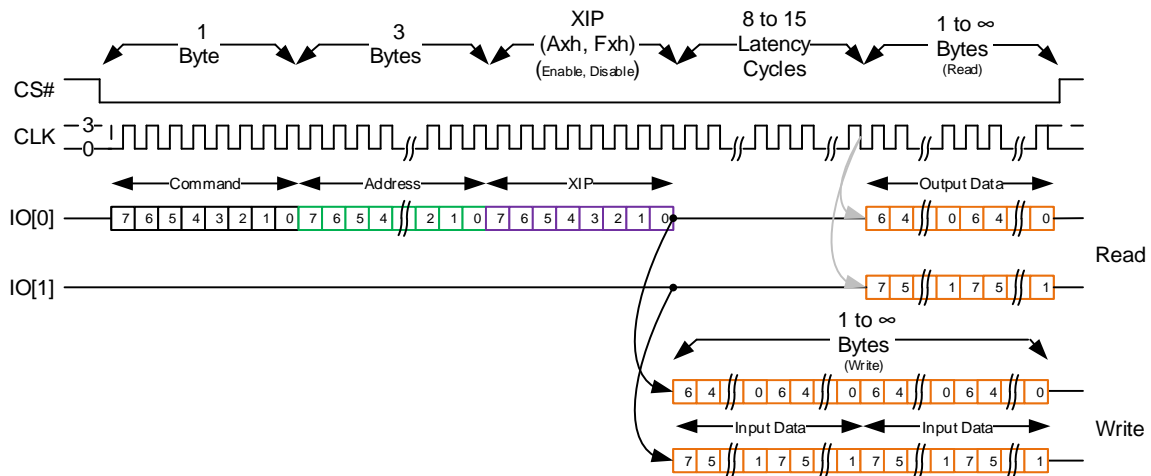
All communication between a host and ASx016A04 is in the form of instructions. Instructions define the operation that must be executed. Instructions consist of a command followed by an optional address modifier and data transfer to or from ASx016A04. All command, address and data information is transferred sequentially. Instructions are structured as follows:

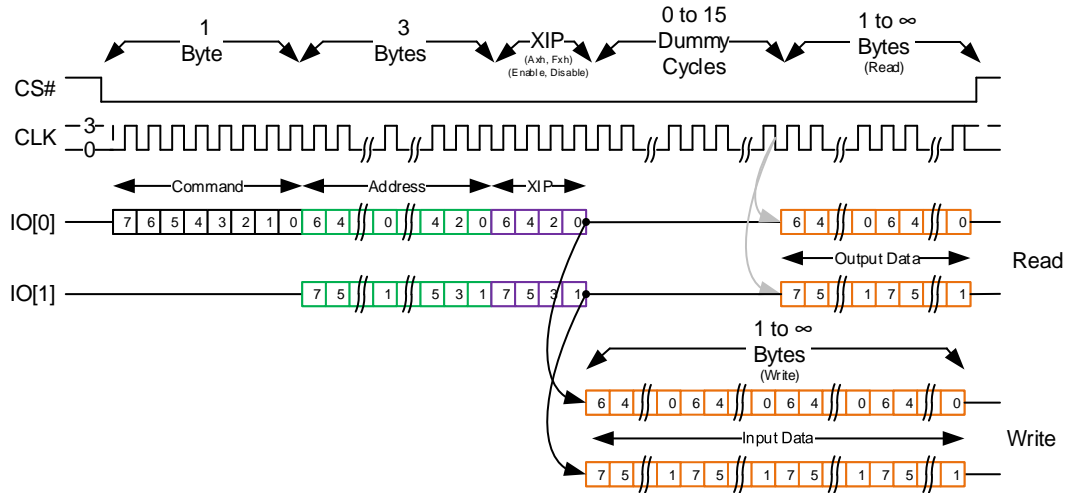
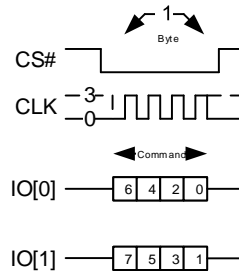
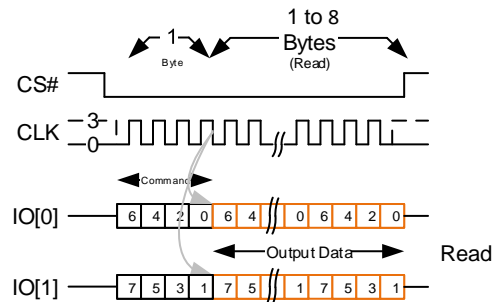
- Each instruction begins with CS# going Low (logic '0') and ends with CS# returning High (Logic '1').
- CLK marks the transfer of each bit.
- Each instructions starts out with an 8-bit command. The command selects the type of operation ASx016A04 must perform. The command is transferred on the rising edges of CLK.
- The command can be stand alone or followed by address to select a memory location or register. The address is always 24-bits wide.
- The address bits are followed by data bits.
- In normal operational mode, Write instructions must be preceded by the WREN instruction. WREN instruction sets the WREN bit in the Status register. WREN bit is reset at the end of every Write instruction. WREN bit can also be reset by executing the WRDI instruction. ASx016A04 offers two other modes, namely SRAM and Back-to-Back Write where WREN does not get reset after a write instruction to the memory array or the augmented storage array. These modes are set in Configuration Register 4.
- ASx016A04 is a high performance serial memory and at higher frequencies, read instructions require latency cycles to compensate for the memory array access time. The number of latency cycles required depends on the operational frequency and is configurable – Configuration Register 2. The latency cycles are inserted after the address bits before the data comes out of ASx016A04.
- For Read and Write instructions, ASx016A04 offers XIP mode. XIP allows similar instructions to be executed sequentially without incurring the command cycles overhead. XIP is enabled by entering byte Axh and disabled by entering byte Fxh. These respective bytes must be entered following the address bits.
- For Read instructions, ASx016A04 offers wrap mode. Wrap bursts are confined to address aligned 16/32/64/128/256 byte boundary. The read address can start anywhere within the wrap boundary. 16/32/64/128/256 wrap configuration is set in Configuration Register 3.
- The entire memory array can be read from or written to using a single read or write instruction. After the starting address is entered, subsequent address are internally incremented as long as CS# is Low and CLK continues to cycle.
- All commands, address and data are shifted with the most significant bit first.

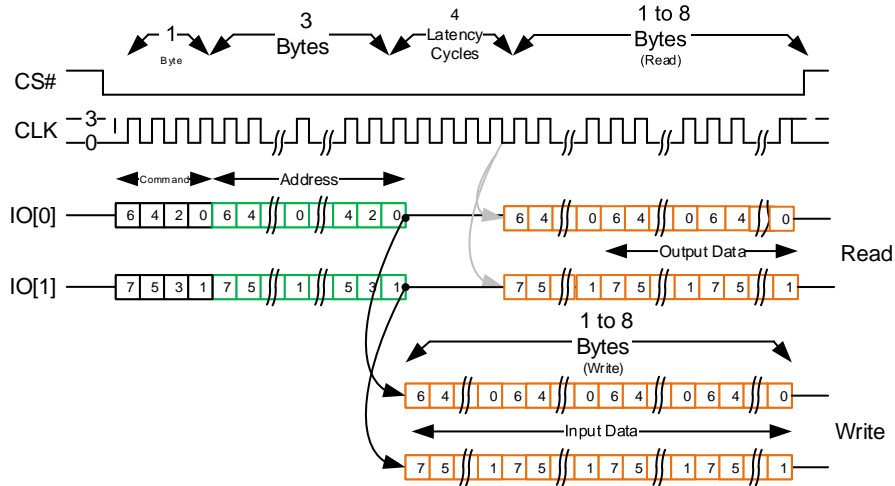
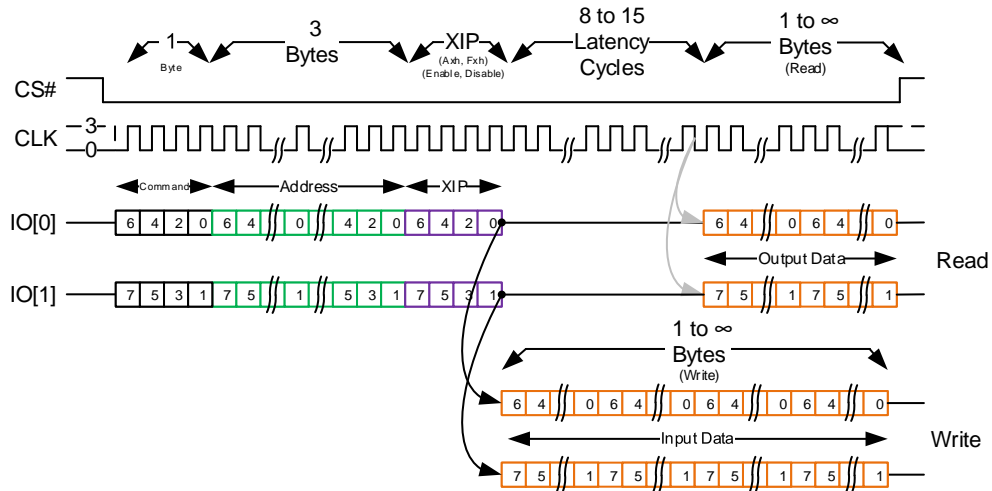
**Figure 8 to Figure 24** show the description of SDR instruction types supported.

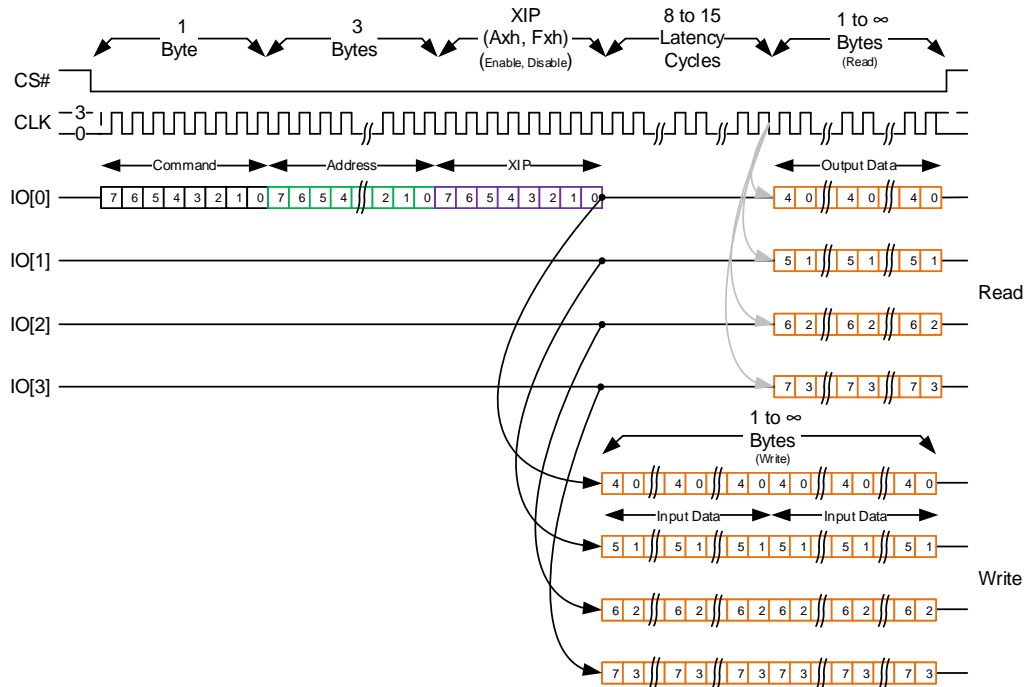
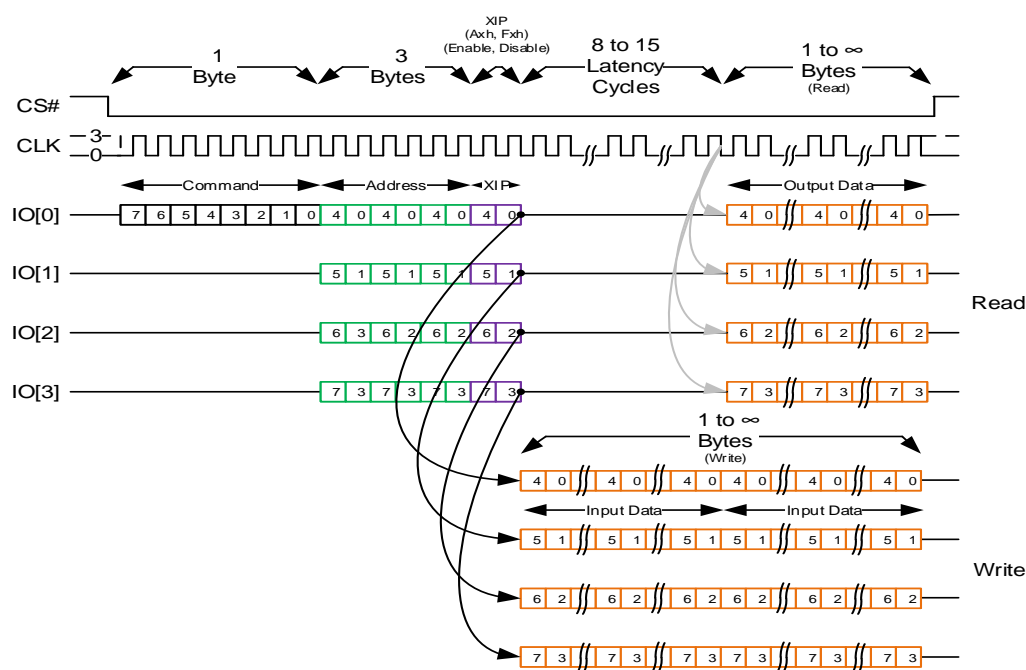
**Figure 8: Description of (1-0-0) Instruction Type**

**Figure 9: Description of (1-0-1) Instruction Type**

**Figure 10: Description of (1-1-1) Instruction Type (Without XIP)**


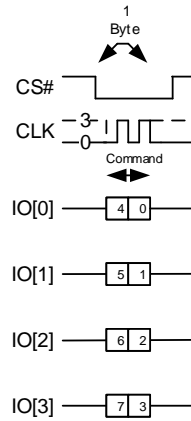
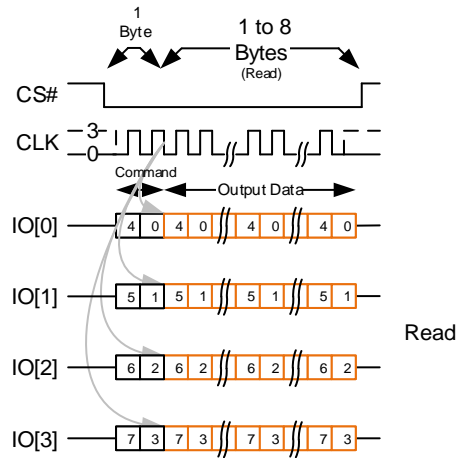


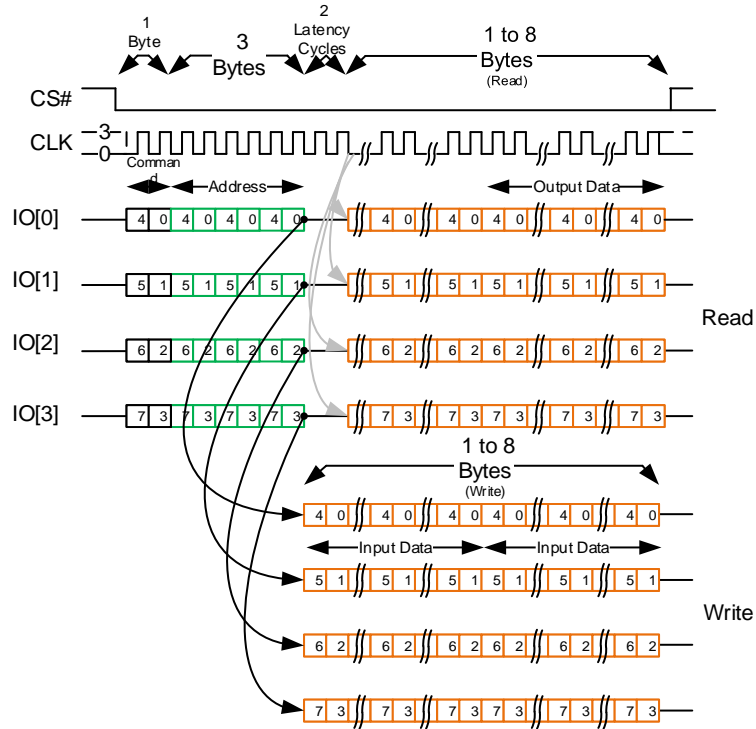
**Figure 11: Description of (1-1-1) Augmented Storage Instruction Type**

**Figure 12: Description of (1-1-1) Instruction Type (With XIP)**

**Figure 13: Description of (1-1-2) Instruction Type (With XIP)**


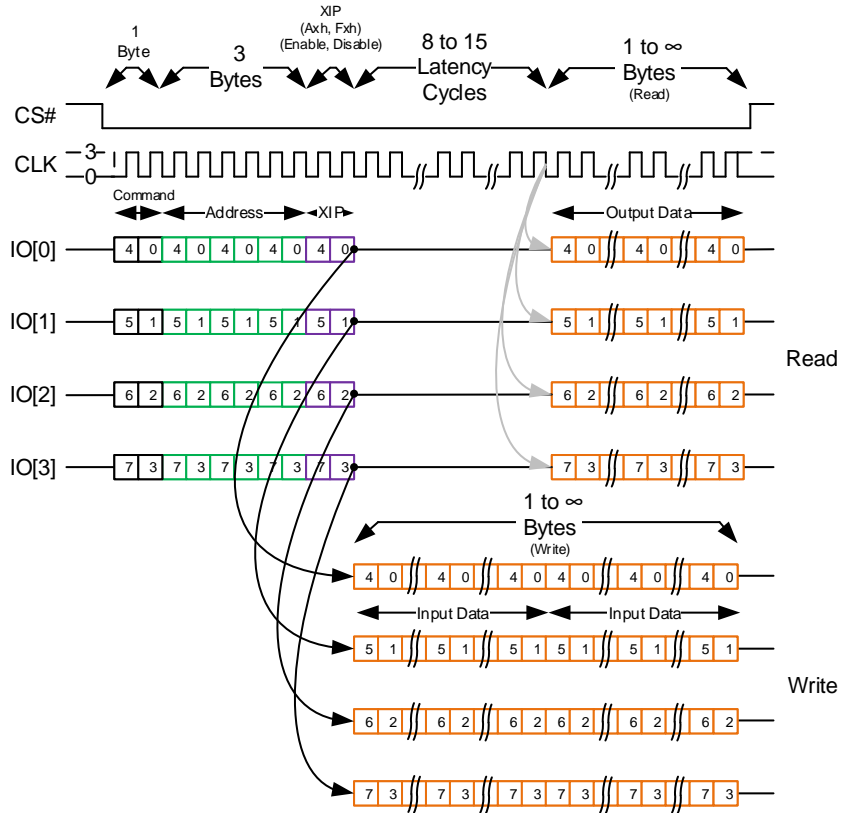
**Figure 14: Description of (1-2-2) Instruction Type (With XIP)**

**Figure 15: Description of (2-0-0) Instruction Type**

**Figure 16: Description of (2-0-2) Instruction Type**


**Figure 17: Description of (2-2-2) Any Register Instruction Type**

**Figure 18: Description of (2-2-2) Instruction Type (With XIP)**


**Figure 19: Description of (1-1-4) Instruction Type (With XIP)**

**Figure 20: Description of (1-4-4) Instruction Type (With XIP)**


**Figure 21: Description of (4-0-0) Instruction Type**

**Figure 22: Description of (4-0-4) Instruction Type**


**Figure 23: Description of (4-4-4) Any Register Instruction Type**


**Figure 24: Description of (4-4-4) Instruction Type (With XIP)**


## Electrical Specifications

**Table 29: Tested Operating Conditions**

| Parameter / Condition                       |                     | Minimum | Typical | Maximum | Units |
|---|---------------------|---------|---------|---------|-------|
| <b>Operating Temperature</b>                | Industrial Extended | -40.0   | -       | 125.0   | °C    |
| <b>V<sub>CC</sub> Supply Voltage (3.0V)</b> | 3.0V                | 2.7     | 3.0     | 3.6     | V     |
| <b>V<sub>CC</sub> Supply Voltage (1.8V)</b> | 1.8V                | 1.71    | 1.8     | 2.0     | V     |
| <b>V<sub>SS</sub> Supply Voltage</b>        |                     | 0.0     | 0.0     | 0.0     | V     |

**Table 30: Pin Capacitance**

| Parameter                     | Test Conditions                                | Symbol             | Maximum | Units |
|-------------------------------|--|--------------------|---------|-------|
| <b>Input Pin Capacitance</b>  | TEMP = 25°C; f = 1 MHz; V <sub>IN</sub> = 3.0V | C <sub>IN</sub>    | 5.0     | pF    |
| <b>Output Pin Capacitance</b> | TEMP = 25°C; f = 1 MHz; V <sub>IN</sub> = 3.0V | C <sub>INOUT</sub> | 6.0     | pF    |

**Table 31: Endurance & Retention**

| Parameter              | Symbol | Test Conditions | Minimum          | Units  |
|------------------------|--------|-----------------|------------------|--------|
| <b>Write Endurance</b> | END    | -               | 10 <sup>16</sup> | cycles |
| <b>Data Retention</b>  | RET    | 125°C           | 10               | years  |
|                        |        | 105°C           | 10               |        |
|                        |        | 85°C            | 1,000            |        |
|                        |        | 75°C            | 10,000           |        |
|                        |        | 65°C            | 1,000,000        |        |



**Table 32: 3.0V DC Characteristics**

| Parameter                 | Symbol              | Test Conditions  | 3.0V Device (2.7V-3.6V) |         |                      | Units |    |
|---------------------------|---------------------|--|-------------------------|---------|----------------------|-------|----|
|                           |                     |  | Minimum                 | Typical | Maximum              |       |    |
| Read Current (1-1-1) SDR  | I <sub>READ1</sub>  | V <sub>CC</sub> = 3.6V, I <sub>OUT</sub> =0mA,<br>CLK=54MHz (V <sub>IL</sub> / V <sub>IH</sub> ),<br>CS#= V <sub>IL</sub> , SI= V <sub>IL</sub> or V <sub>IH</sub> | -                       | 8       | 9                    | mA    |    |
| Read Current (2-2-2) SDR  | I <sub>READ2</sub>  |  | -                       | 9       | 10                   | mA    |    |
| Read Current (4-4-4) SDR  | I <sub>READ3</sub>  |  | -                       | 10      | 12                   | mA    |    |
| Write Current (1-1-1) SDR | I <sub>WRITE1</sub> | V <sub>CC</sub> = 3.6V, I <sub>OUT</sub> =0mA,<br>CLK=54MHz (V <sub>IL</sub> / V <sub>IH</sub> ),<br>CS#= V <sub>IL</sub> , SI= V <sub>IL</sub> or V <sub>IH</sub> | -                       | 14      | 16                   | mA    |    |
| Write Current (2-2-2) SDR | I <sub>WRITE2</sub> |  | -                       | 17      | 20                   | mA    |    |
| Write Current (4-4-4) SDR | I <sub>WRITE3</sub> |  | -                       | 22      | 25                   | mA    |    |
| Standby Current           | I <sub>SB</sub>     | V <sub>CC</sub> = 3.6V, CLK=V <sub>CC</sub> ,<br>CS#=V <sub>CC</sub> , SI=V <sub>CC</sub>  | Ta = 25°C               | -       | 160                  | -     | µA |
|                           |                     |  | Ta = 85°C               | -       | -                    | 400   | µA |
|                           |                     |  | Ta =105°C               | -       | -                    | 600   | µA |
| Deep Power Down Current   | I <sub>DPD</sub>    | V <sub>CC</sub> = 3.6V, CLK=V <sub>CC</sub> , CS#=V <sub>CC</sub> , SI=V <sub>CC</sub>   | -                       | 5       | 25                   | µA    |    |
| Hibernate Current         | I <sub>HBN</sub>    | V <sub>CC</sub> = 3.6V, CLK=V <sub>CC</sub> , CS#=V <sub>CC</sub> , SI=V <sub>CC</sub>   | -                       | 0.1     | -                    | µA    |    |
| Input Leakage Current     | I <sub>LI</sub>     | V <sub>IN</sub> =0 to V <sub>CC</sub> (max)  | -                       | -       | ±1.0                 | µA    |    |
| Output Leakage Current    | I <sub>LO</sub>     | V <sub>OUT</sub> =0 to V <sub>CC</sub> (max)   | -                       | -       | ±1.0                 | µA    |    |
| Input High Voltage        | V <sub>IH</sub>     |  | 0.7xV <sub>CC</sub>     | -       | V <sub>CC</sub> +0.3 | V     |    |
| Input Low Voltage         | V <sub>IL</sub>     |  | -0.3                    | -       | 0.3xV <sub>CC</sub>  | V     |    |
| Output High Voltage Level | V <sub>OH</sub>     | I <sub>OH</sub> = -100µA   | V <sub>CC</sub> -0.2    | -       | -                    | V     |    |
|                           |                     | I <sub>OH</sub> = -1mA   | 2.4                     | -       | -                    | V     |    |
| Output Low Voltage Level  | V <sub>OL</sub>     | I <sub>OL</sub> = 150µA  | -                       | -       | 0.2                  | V     |    |
|                           |                     | I <sub>OL</sub> = 2mA  | -                       | -       | 0.4                  | V     |    |

**Table 33: 1.8V DC Characteristics**

| Parameter                 | Symbol              | Test Conditions  | 1.8V Device (1.71V-2.0V) |         |         | Units |    |
|---------------------------|---------------------|--|--------------------------|---------|---------|-------|----|
|                           |                     |  | Minimum                  | Typical | Maximum |       |    |
| Read Current (1-1-1) SDR  | I <sub>READ1</sub>  | V <sub>CC</sub> = 2.0V, I <sub>OUT</sub> =0mA,<br>CLK=54MHz (V <sub>IL</sub> / V <sub>IH</sub> ),<br>CS#= V <sub>IL</sub> , SI= V <sub>IL</sub> or V <sub>IH</sub> | -                        | 5       | 8       | mA    |    |
| Read Current (2-2-2) SDR  | I <sub>READ2</sub>  |  | -                        | 6       | 9       | mA    |    |
| Read Current (4-4-4) SDR  | I <sub>READ3</sub>  |  | -                        | 7       | 11      | mA    |    |
| Write Current (1-1-1) SDR | I <sub>WRITE1</sub> | V <sub>CC</sub> = 2.0V, I <sub>OUT</sub> =0mA,<br>CLK=54MHz (V <sub>IL</sub> / V <sub>IH</sub> ),<br>CS#= V <sub>IL</sub> , SI= V <sub>IL</sub> or V <sub>IH</sub> | -                        | 13      | 15      | mA    |    |
| Write Current (2-2-2) SDR | I <sub>WRITE2</sub> |  | -                        | 16      | 19      | mA    |    |
| Write Current (4-4-4) SDR | I <sub>WRITE3</sub> |  | -                        | 20      | 23      | mA    |    |
| Standby Current           | I <sub>SB</sub>     | V <sub>CC</sub> = 2.0V, CLK=V <sub>CC</sub> ,<br>CS#=V <sub>CC</sub> , SI=V <sub>CC</sub>  | Ta = 25°C                | -       | 140     | -     | µA |
|                           |                     |  | Ta = 85°C                | -       | -       | 350   | µA |
|                           |                     |  | Ta=105°C                 | -       | -       | 500   | µA |

| Parameter                 | Symbol             | Test Conditions  | 1.8V Device (1.71V-2.0V) |         |                      | Units |
|---------------------------|--------------------|--|--------------------------|---------|----------------------|-------|
|                           |                    |  | Minimum                  | Typical | Maximum              |       |
| Deep Power Down Current   | I <sub>DPD</sub>   | V <sub>CC</sub> = 2.0V, CLK=V <sub>CC</sub> , CS#=V <sub>CC</sub> , SI=V <sub>CC</sub> | -                        | 4       | 20                   | μA    |
| Hibernate Current         | I <sub>HBN</sub>   | V <sub>CC</sub> = 2.0V, CLK=V <sub>CC</sub> , CS#=V <sub>CC</sub> , SI=V <sub>CC</sub> | -                        | 0.1     | -                    | μA    |
| Input Leakage Current     | I <sub>LI</sub>    | V <sub>IN</sub> =0 to V <sub>CC</sub> (max)  | -                        | -       | ±1.0                 | μA    |
| WP# Leakage Current       | I <sub>WP#LI</sub> | V <sub>IN</sub> =0 to V <sub>CC</sub> (max)  | -100.0                   | -       | +1.0                 | μA    |
| Output Leakage Current    | I <sub>LO</sub>    | V <sub>OUT</sub> =0 to V <sub>CC</sub> (max)   | -                        | -       | ±1.0                 | μA    |
| Input High Voltage        | V <sub>IH</sub>    |  | 0.7xV <sub>CC</sub>      | -       | V <sub>CC</sub> +0.3 | V     |
| Input Low Voltage         | V <sub>IL</sub>    |  | -0.3                     | -       | 0.3xV <sub>CC</sub>  | V     |
| Output High Voltage Level | V <sub>OH</sub>    | I <sub>OH</sub> = -100μA   | V <sub>CC</sub> -0.2     | -       | -                    | V     |
|                           |                    | I <sub>OH</sub> = -1mA   | 1.5                      | -       | -                    | V     |
| Output Low Voltage Level  | V <sub>OL</sub>    | I <sub>OL</sub> = 150μA  | -                        | -       | 0.2                  | V     |
|                           |                    | I <sub>OL</sub> = 2mA  | -                        | -       | 0.4                  | V     |

## Absolute Maximum Ratings

Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only. Exposure to maximum rating for extended periods may adversely affect reliability.

**Table 34: Absolute Maximum Ratings**

| Parameter   | Minimum    | Maximum | Units |
|---|------------|---------|-------|
| Magnetic Field During Write                                   | ---        | 24000   | A/m   |
| Magnetic Field During Read                                    | ---        | 24000   | A/m   |
| Junction Temperature  | ---        | 125     | °C    |
| Storage Temperature   | -55 to 150 |         | °C    |
| ESD HBM (Human Body Model)<br>ANSI/ESDA/JEDEC JS-001-2017     | ≥  2000 V  |         | V     |
| ESD CDM (Charged Device Model)<br>ANSI/ESDA/JEDEC JS-002-2018 | ≥  500 V   |         | V     |
| Latch-Up (I-test)<br>JESD78                                   | ≥  100 mA  |         | mA    |
| Latch-Up (Vsupply over-voltage test)<br>JESD78                | Passed     |         | ---   |

**Table 35: AC Test Conditions**

| Parameter                                  | Value                   |
|--|-------------------------|
| Input pulse levels                         | 0.0V to V <sub>CC</sub> |
| Input rise and fall times                  | 3.0ns                   |
| Input and output measurement timing levels | V <sub>CC</sub> /2      |
| Output Load                                | CL = 30.0pF             |

## CS# Operation & Timing

Figure 25: CS# Operation & Timing

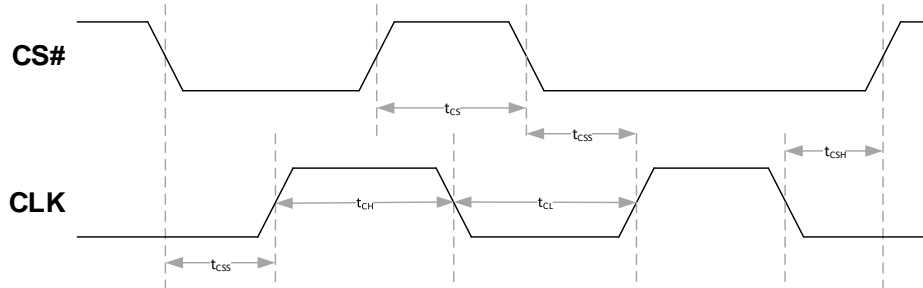


Table 36: CS# Operation

| Parameter  | Symbol    | Minimum              | Maximum | Units   |
|--|-----------|----------------------|---------|---------|
| <b>Clock Frequency</b>   | $f_{CLK}$ | 1                    | 54      | MHz     |
| <b>Clock Low Time</b>  | $t_{CL}$  | $0.45 * 1 / f_{CLK}$ | -       | ns      |
| <b>Clock High Time</b>   | $t_{CH}$  | $0.45 * 1 / f_{CLK}$ | -       | ns      |
| <b>Chip Deselect Time after Read Cycle</b>                       | $t_{CS1}$ | 20                   | -       | ns      |
| <b>Chip Deselect Time after Register Write Cycle<sup>1</sup></b> | $t_{CS2}$ | 5                    | -       | $\mu s$ |
| <b>Chip Deselect Time after Write Cycle (SPI)</b>                | $t_{CS3}$ | 280                  | -       | ns      |
| <b>Chip Deselect Time after Write Cycle (DPI)</b>                | $t_{CS4}$ | 350                  | -       | ns      |
| <b>Chip Deselect Time after Write Cycle (QPI)</b>                | $t_{CS5}$ | $490^2$              | -       | ns      |
| <b>CS# Setup Time (w.r.t CLK)</b>                                | $t_{CSS}$ | 5                    | -       | ns      |
| <b>CS# Hold Time (w.r.t CLK)</b>                                 | $t_{CSH}$ | 4                    | -       | ns      |

**Notes:**

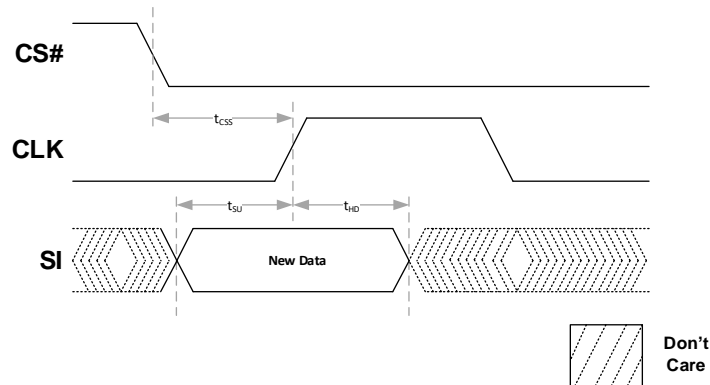
Power supplies must be stable

1:SDR operation only

2:For single byte operations,  $t_{CS5}$  is 280ns

## Command, Address, XIP and Data Input Operation & Timing

Figure 26: SDR Command, Address and Data Input Operation & Timing

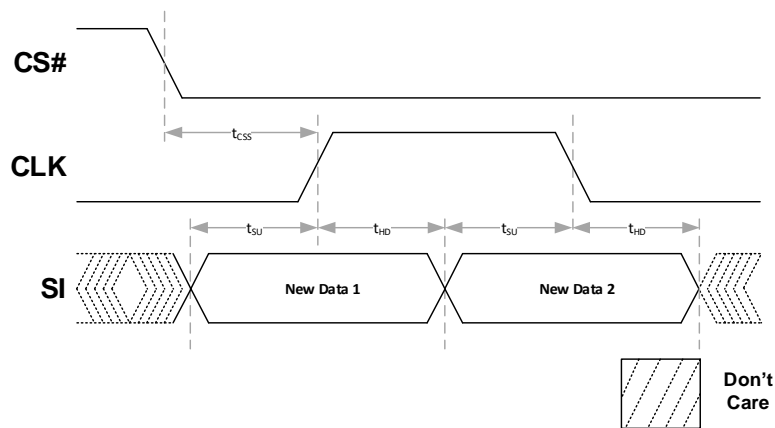


**Table 37: SDR Command, Address, XIP, and Data Input Operation & Timing**

| Parameter                   | Symbol   | Minimum | Maximum | Units |
|-----------------------------|----------|---------|---------|-------|
| Data Setup Time (w.r.t CLK) | $t_{SU}$ | 2.0     | -       | ns    |
| Data Hold Time (w.r.t CLK)  | $t_{HD}$ | 3.0     | -       | ns    |

**Notes:**

Power supplies must be stable

**Figure 27: DDR Command, Address and Data Input Operation & Timing**

**Table 38: DDR Command, Address, XIP, and Data Input Operation & Timing**

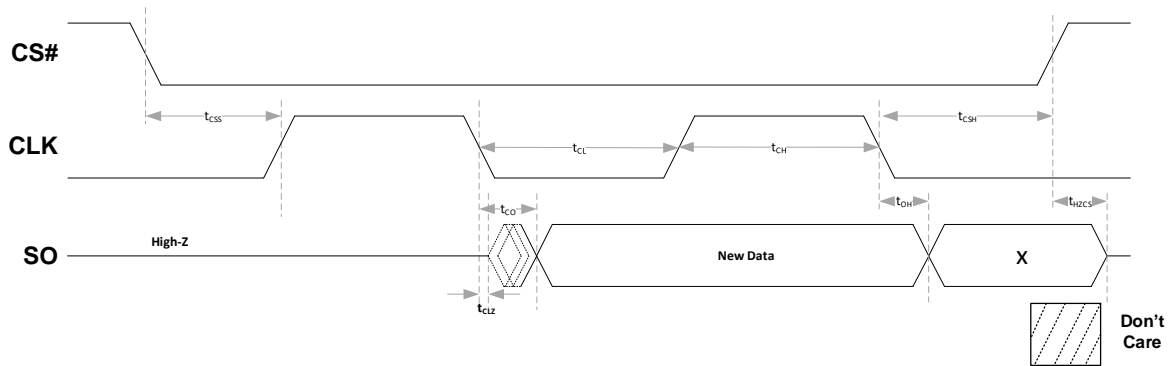
| Parameter                   | Symbol   | Minimum | Maximum | Units |
|-----------------------------|----------|---------|---------|-------|
| Data Setup Time (w.r.t CLK) | $t_{SU}$ | 4.0     | -       | ns    |
| Data Hold Time (w.r.t CLK)  | $t_{HD}$ | 4.0     | -       | ns    |

**Notes:**

Power supplies must be stable

## Data Output Operation & Timing

**Figure 28: SDR Data Output Operation & Timing**



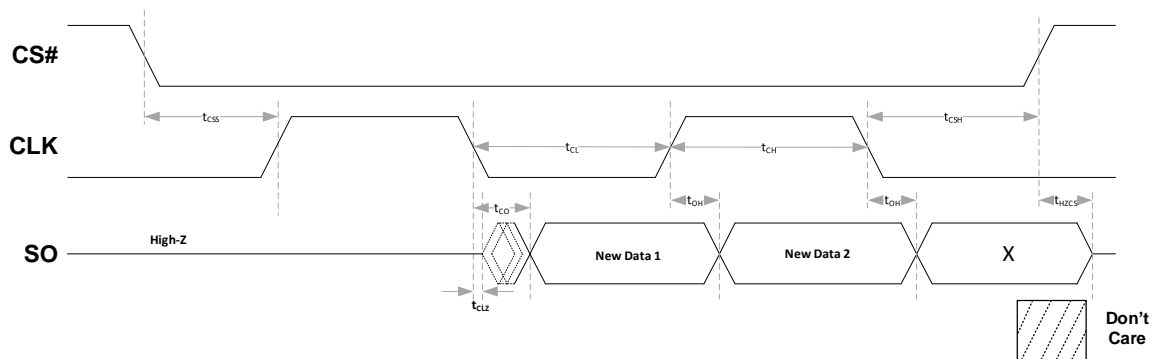
**Table 39: SDR Data Output Operation & Timing**

| Parameter                        | Symbol     | Minimum | Maximum | Units |
|----------------------------------|------------|---------|---------|-------|
| CLK Low to Output Low Z (Active) | $t_{CLZ}$  | 0       | -       | ns    |
| Output Valid (w.r.t CLK)         | $t_{CO}$   | -       | 7.0     | ns    |
| Output Hold Time (w.r.t CLK)     | $t_{OH}$   | 1.0     | -       | ns    |
| Output Disable Time (w.r.t CS#)  | $t_{HZCS}$ | -       | 7.0     | ns    |

**Notes:**

Power supplies must be stable

**Figure 29: DDR Data Output Operation & Timing**



**Table 40: DDR Data Output Operation & Timing**

| Parameter                        | Symbol     | Minimum | Maximum | Units |
|----------------------------------|------------|---------|---------|-------|
| CLK Low to Output Low Z (Active) | $t_{CLZ}$  | 0       | -       | ns    |
| Output Valid (w.r.t CLK)         | $t_{CO}$   | -       | 7.0     | ns    |
| Output Hold Time (w.r.t CLK)     | $t_{OH}$   | 1.0     | -       | ns    |
| Output Disable Time (w.r.t CS#)  | $t_{HZCS}$ | -       | 6.0     | ns    |

**Notes:**

Power supplies must be stable

## WP# Operation & Timing

Figure 30: WP# Operation & Timing

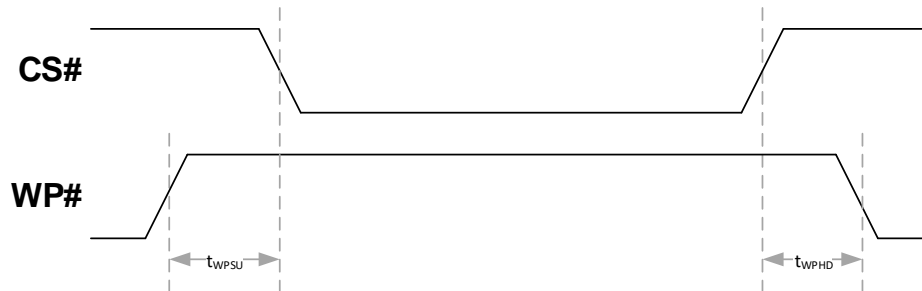


Table 41: WP# Operation & Timing

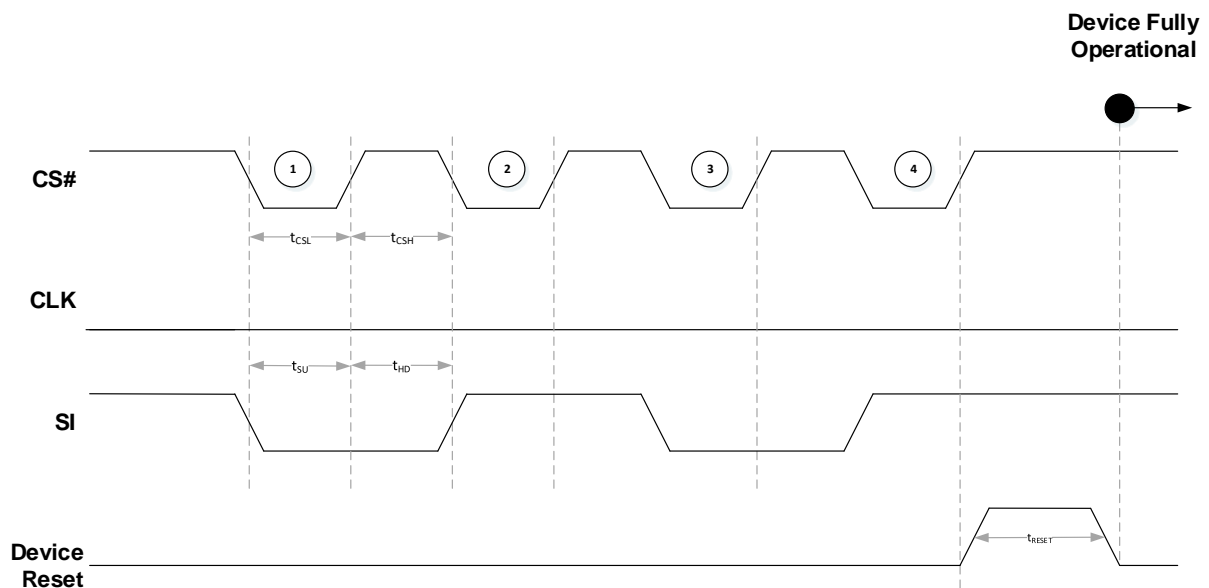
| Parameter                  | Symbol     | Minimum | Maximum | Units |
|----------------------------|------------|---------|---------|-------|
| WP# Setup Time (w.r.t CS#) | $t_{WPSU}$ | 20      | -       | ns    |
| WP# Hold Time (w.r.t CS#)  | $t_{WPHD}$ | 20      | -       | ns    |

**Notes:**

Power supplies must be stable

## JEDEC Reset Operation & Timing

Figure 31: JEDEC Reset Operation & Timing



**Table 42: JEDEC Reset Operation & Timing**

| Parameter                         | Symbol             | Minimum | Maximum | Units |
|-----------------------------------|--------------------|---------|---------|-------|
| <b>CS# Low Time</b>               | t <sub>CL</sub>    | 1.0     | -       | μs    |
| <b>CS# High Time</b>              | t <sub>CH</sub>    | 1.0     | -       | μs    |
| <b>SI Setup Time (w.r.t CS#)</b>  | t <sub>SU</sub>    | 5.0     | -       | ns    |
| <b>SI Hold Time (w.r.t CS#)</b>   | t <sub>HD</sub>    | 5.0     | -       | ns    |
| <b>JEDEC Hardware Reset</b>       | t <sub>RESET</sub> | -       | 450.0   | μs    |
| <b>Software Reset<sup>1</sup></b> | t <sub>SRST</sub>  | -       | 50.0    | μs    |

**Notes:**

Power supplies must be stable

1: Software Reset timing is for Instruction based Reset (SRST)

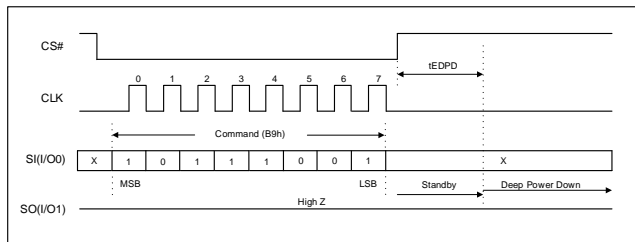


## Enter Deep Power Down Command (EDP – B9h)

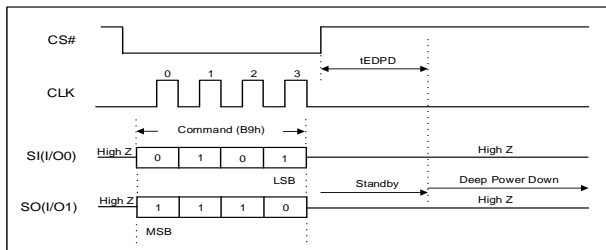
The command sequences are shown below. Executing the Enter Deep Power down (EDP) command is the only way to put the device in the deep power down mode. The device consumption drops to  $I_{DP}$ .

The deep power down mode subsequently reduces the standby current from  $I_{SB}$  to  $I_{DP}$ . No other command must be issued while the device is in deep power down mode.

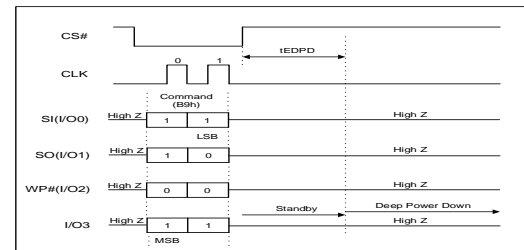
To enter the deep power down mode, CS# is driven low, following the enter deep power down (EDPD) command, CS# must be driven high after the eighth bit of the command code has been latched in or the EDP command will not be executed. After CS# is driven high, it requires a delay of  $t_{EDPD}$  (Table 6 and 7) before the supply current is reduced to  $I_{DP}$  and the Deep Power Down mode is entered. The command can be issued in SPI or QPI modes.



**Figure 32: Enter Deep Power Down in SPI Command Sequence**



**Figure 39: Enter Deep Power Down in DPI Command Sequence**

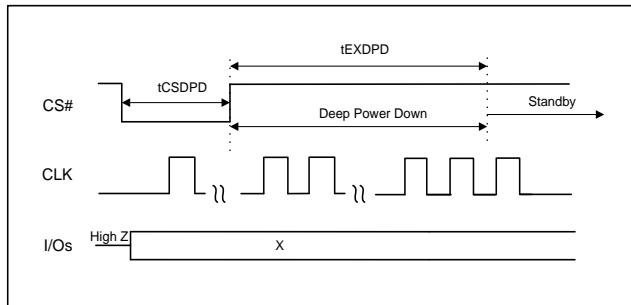


**Figure 40: Enter Deep Power Down in QPI Command Sequence**

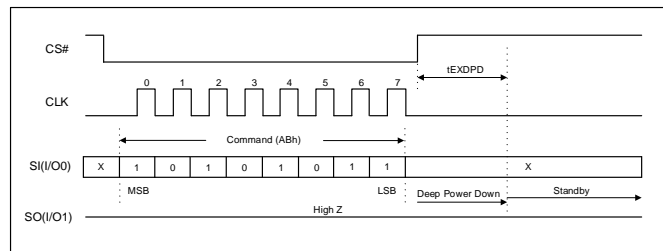
## Exit Deep Power Down Command (EXDPD - ABh)

The command sequences are shown below. There are two ways to exit deep power down mode:

1. Toggling CS# with a CS# pulse width of  $t_{\text{CSDPD}}$  while CLK and I/Os are Don't Care. During waking up from deep power down, I/Os remain to be in high Z.
2. Driving CS# low follows with the Exit Deep Power Down (EXDPD) command. CS# must be driven high after the eight bit of the command code has been latched in or the EXDPD command will not executed.

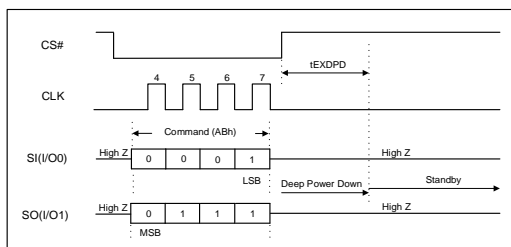


**Figure 41: Exit Deep Power Down by Toggling CS#**

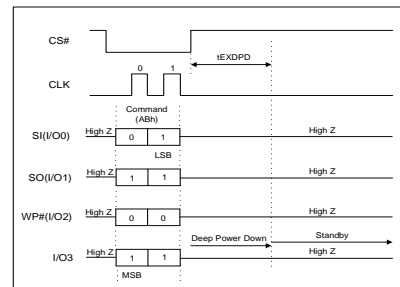


**Figure 42: Exit Deep Power Down in SPI Command Sequence**

It requires a delay of  $t_{\text{EXDPD}}$  (Table 6 and 7) before the device can fully exit the deep power down mode and enter standby mode. The command can be issued in SPI, DPI, and QPI mode. Status of all non-volatile bits in registers remains unchanged when the device enters or exits the deep power down mode.



**Figure 43: Exit Deep Power Down in DPI Command Sequence**



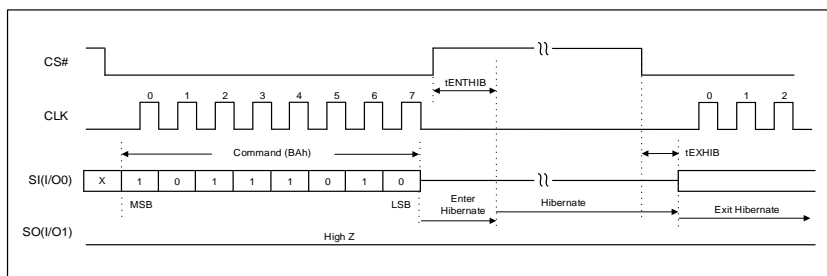
**Figure 44: Exit Deep Power Down in QPI Command Sequence**

## Enter Hibernate Command (EHBN – BAh)

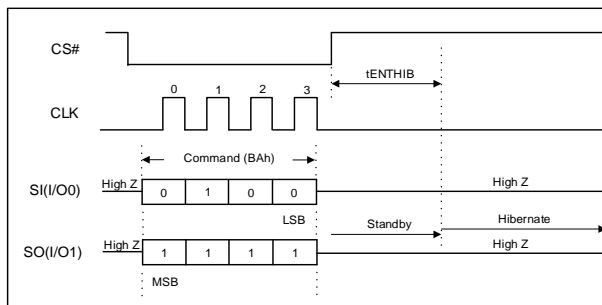
The command sequences are shown below. Executing the Enter Hibernate command is the only way to put the device in the hibernate mode. The device drops down to the lowest power consumption mode:  $I_{HBN}$ . When in hibernate mode, the CLK and SI pins are ignored and SO will be high-Z.

To enter the hibernate mode, CS# is driven low, following the Enter Hibernate (EHBN) command. After CS# is driven high, it requires a delay of  $t_{ENTHIB}$  time (Table 6 and 7) before the supply current is reduced to  $I_{HBN}$  and hibernate mode is entered.

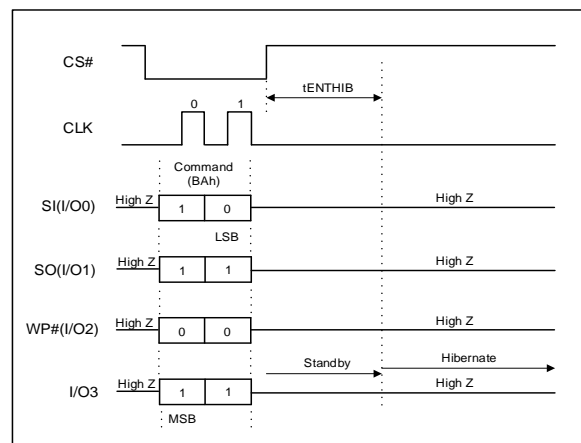
Toggling CS# (low to high) will return the device to standby mode. The command can be issued in SPI, DPI, and QPI modes.



**Figure 45: Enter Hibernate in SPI Command Sequence**



**Figure 46: Enter Hibernate in DPI Command Sequence**



**Figure 47: Enter Hibernate in QPI Command Sequence**

## Thermal Resistance

**Table 43: Thermal Resistance**

| Parameter     | Description                              | Test Conditions   | 8-pad WSON | 8-pin SOIC | Unit |
|---------------|--|---|------------|------------|------|
| $\theta_{JA}$ | Thermal resistance (junction to ambient) | Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51 | 43.67      | 53.59      | °C/W |
| $\theta_{JC}$ | Thermal resistance (junction to case)    |   | 18.54      | 4.29       |      |

**Notes:**

1: These parameters are guaranteed by characterization; not tested in production.

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## Revision History

| Revision     | Date                     | Change Summary  |
|--------------|--------------------------|---|
| <b>REV J</b> | 03/04/2020               | Added ESD and Latch-up specifications (Table 36).<br>Corrected table numbering.<br>Removed 3 rows on Table 23 with latency and changed to 50MHz for 108.<br>Table 28: Instructions Set<br>Read 03h: Removed 2-2-2, 4-4-4 and latency cycles dots, freq=50MHz<br>Write 02h: Removed 2-2-2 and 4-4-4 dots.<br>RDAS 4Bh: Added latency cycles dot, removed 2-2-2 and 4-4-4 dots, freq=50MHz<br>WRAS 42h: Removed 2-2-2 and 4-4-4 dots.<br>Added Table 24 for Augment Storage Array Read Latency vs Max Frequency.<br>Removed Augmented Storage Protection Register from Table 11.<br>Added Augmented Storage (1-1-1) Figure 12.<br>Changed 2-2-2 and 4-4-4 (Figure 18 and 24) to Any Register Instruction diagrams.<br>Changed all XIP diagrams from 0-15 dummy cycles to 8-15 latency cycles.<br>Removed 0-15 dummy cycles from 1-1-1 without XIP (Figure 11).<br>Changed tCSDPD to 50ns in Table 6 and Table 7.<br>Removed Advanced from the footer. |
| <b>REV K</b> | 06/03/2020               | Swapped Standby and Deep Power Down in Figure 38.<br>Removed mode in Figures 39, 45 and 46.<br>Added junction and storage temperature specifications.<br>Combined magnetic immunity and ESD tables.<br>Updated burn-in specification and part numbers.<br>Removed Serial Number Register from Table 11.<br>Updated latency values in Table 22.<br>Updated Icc and Isb values in Tables 32 and 33.<br>Updated chip deselect values in Table 36 and Note 1.<br>Added note 7 for Table 28.   |
| <b>REV L</b> | 07/17/2020               | Updated Icc values in Tables 32 and 33.<br>Corrected Figures 38 and 42.   |
| <b>REV M</b> | 09/11/2020               | Removed 1Mb, 4Mb, 8Mb densities and BGA package options.<br>Changed the burn in temperature to 125°C.<br>Changed Endurance to 10 <sup>14</sup> write cycles.<br>Added thermal resistance specifications.  |
| <b>REV N</b> | 10/08/2020               | Removed 108MHz operation, DDR mode<br>Changed Endurance back to 10 <sup>16</sup><br>Updated Ordering Part Number decoder and valid product OPN table  |
| <b>REV O</b> | 07/16/2021               | Added REACH Compliance<br>Updated Product Use Limitations   |
| <b>REV P</b> | 03/15/2022<br>05/18/2022 | Corrected Manufacturer ID Temp field from 0002 to 0010<br>Fixed Spelling Mistake  |
| <b>REV Q</b> | 07/27/2022               | Removed Performance Table<br>Added Figures to ToC<br>Added Tables to ToC<br>Updated Power Down Behavior Diagram   |

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| Revision | Date       | Change Summary  |
|----------|------------|---|
|          |            | Updated Power Down/Power Up description<br>Added VCCRST parameter<br>Added V <sub>CC</sub> Ramp Down Time (max)<br>Updated SDR Data Output Operation & Timing<br>Updated DDR Data Output Operation & Timing |
| REV R    | 10/04/2022 | Removed V <sub>CC</sub> Ramp Down Time (max)  |